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Shrivastava

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(54) **METHODS AND APPARATUS FOR LOW INPUT VOLTAGE BANDGAP REFERENCE ARCHITECTURE AND CIRCUITS**

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(21) Appl. No.: **14/880,817**

(22) Filed: **Oct. 12, 2015**

(65) **Prior Publication Data**

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Related U.S. Application Data

(63) Continuation of application No. 14/454,342, filed on Aug. 7, 2014, now Pat. No. 9,158,320, and a continuation of application No. PCT/US2015/043986, filed on Aug. 6, 2015.

(51) **Int. Cl.**

G05F 1/46	(2006.01)
G05F 3/30	(2006.01)
G05F 3/18	(2006.01)

(52) **U.S. Cl.**

CPC ***G05F 1/468*** (2013.01); ***G05F 3/18*** (2013.01); ***G05F 3/30*** (2013.01)

(58) **Field of Classification Search**

CPC ... G05F 3/18; G05F 3/13; G05F 3/262; G05F 3/247; G05F 1/468; G05F 1/46; G05F 3/30

See application file for complete search history.

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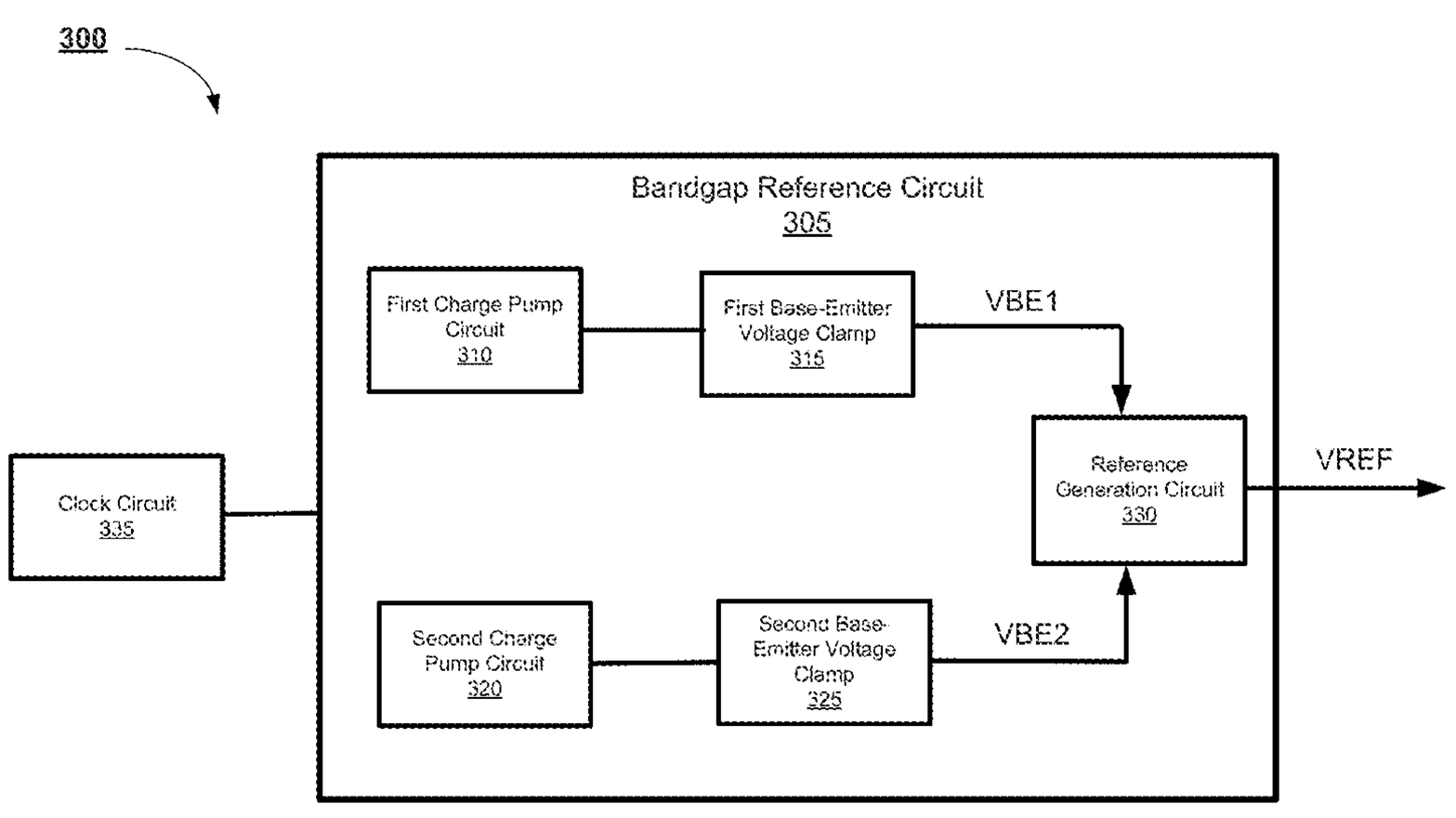
(57) **ABSTRACT**

In some embodiments, an apparatus includes a bandgap reference circuit having a first bipolar junction transistor (BJT) that can receive a current from a node having a terminal voltage and can output a base emitter voltage. The apparatus also includes a second bipolar junction transistor (BJT) having a device width greater than a device width of the first BJT. The second BJT can receive a current from a node having a terminal voltage and output a base emitter voltage. In such embodiments, the apparatus also includes a reference generation circuit operatively coupled to the first BJT and the second BJT, where the reference generation circuit can generate a bandgap reference voltage based on the base emitter voltage of the first BJT and the base emitter voltage of the second BJT.

20 Claims, 19 Drawing Sheets



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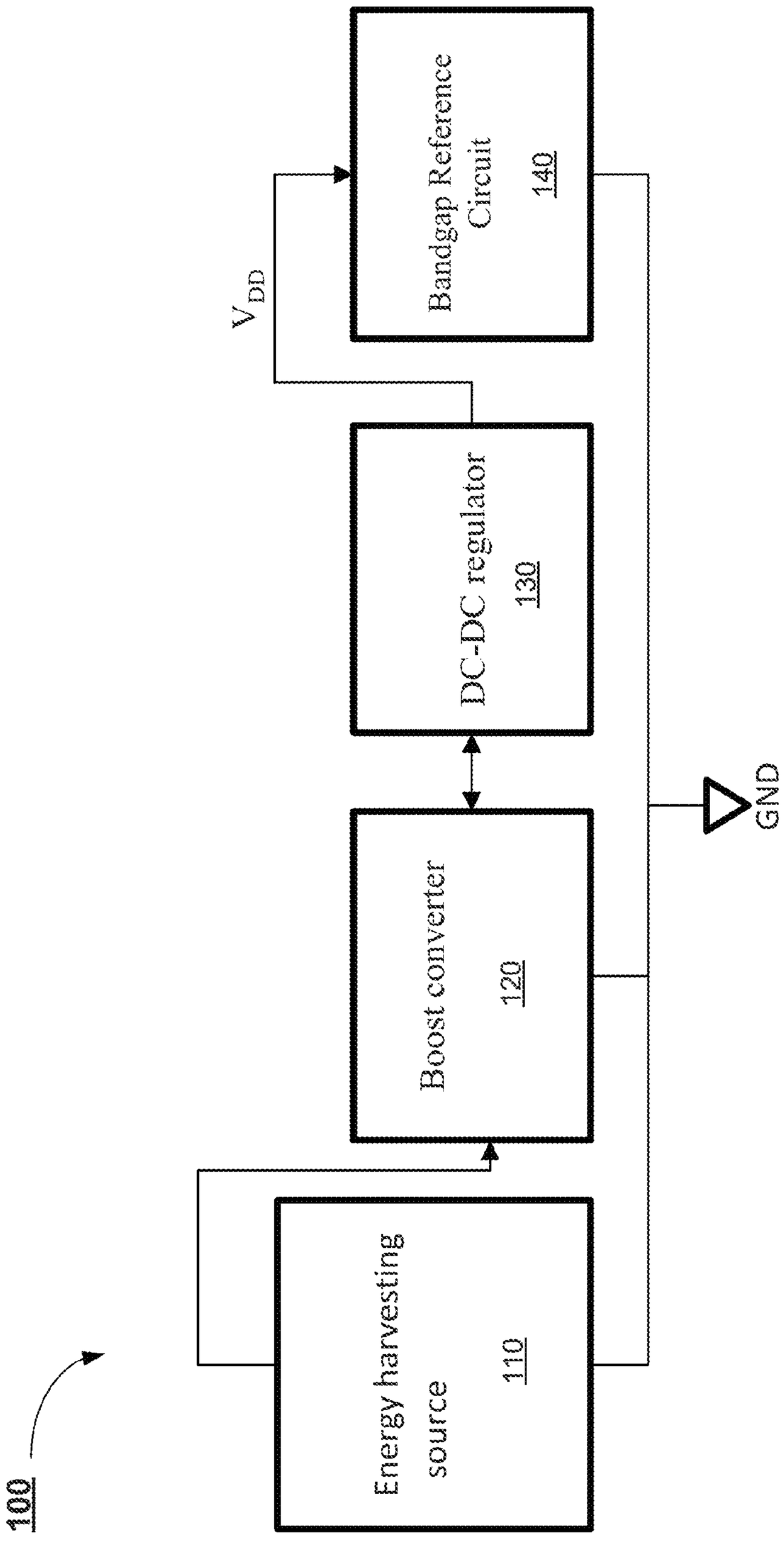

100
Energy harvesting source
110
Boost converter
120
DC-DC regulator
130
Bandgap Reference Circuit
140
V_{DD}
GND

FIG. 1

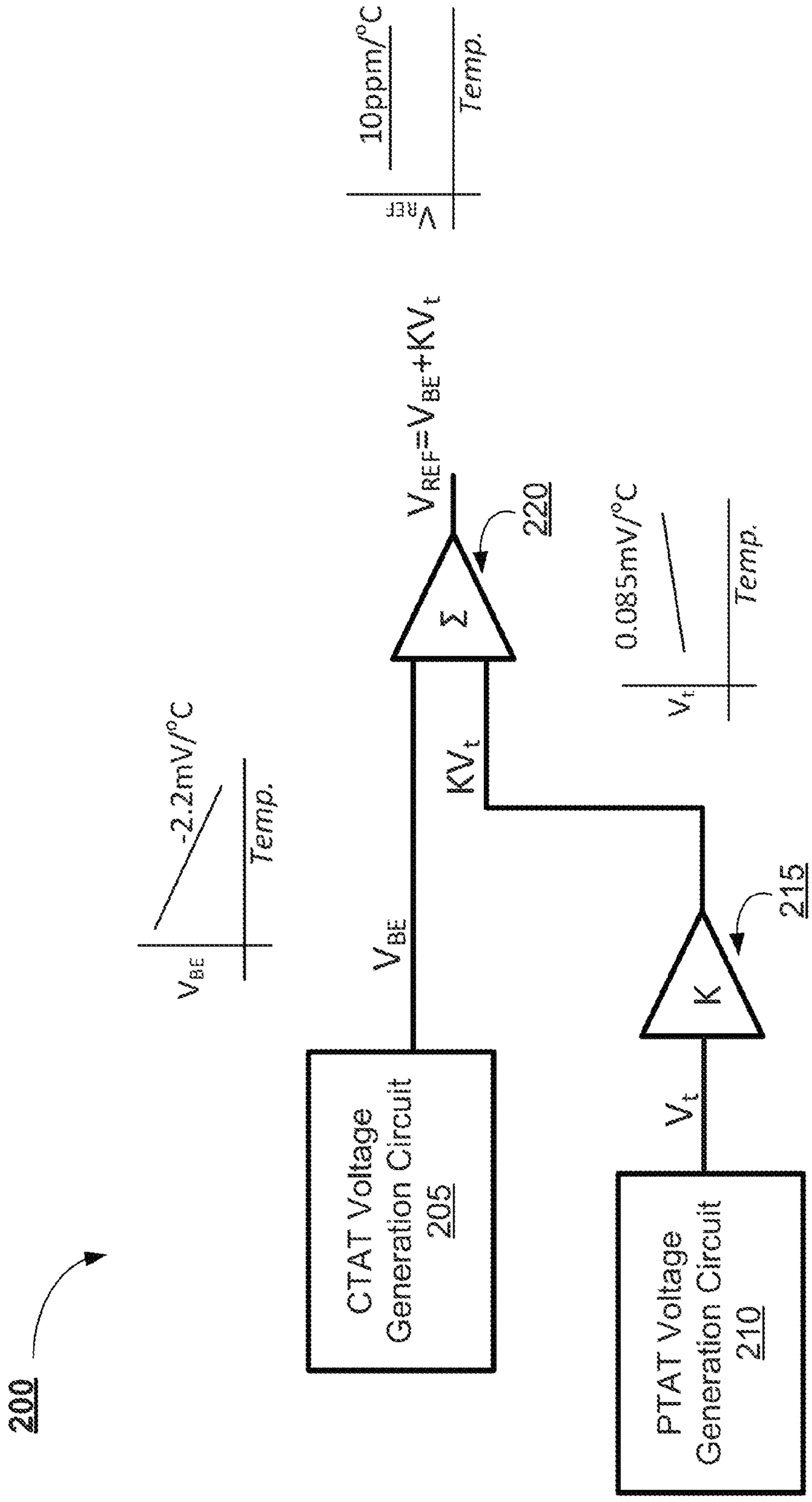

200
CTAT Voltage Generation Circuit 205
PTAT Voltage Generation Circuit 210
215
220
K
Σ
V_{BE}
V_t
KV_t
$V_{REF}=V_{BE}+KV_t$
-2.2mV/°C
Temp.
0.085mV/°C
Temp.
10ppm/°C
Temp.

FIG. 2

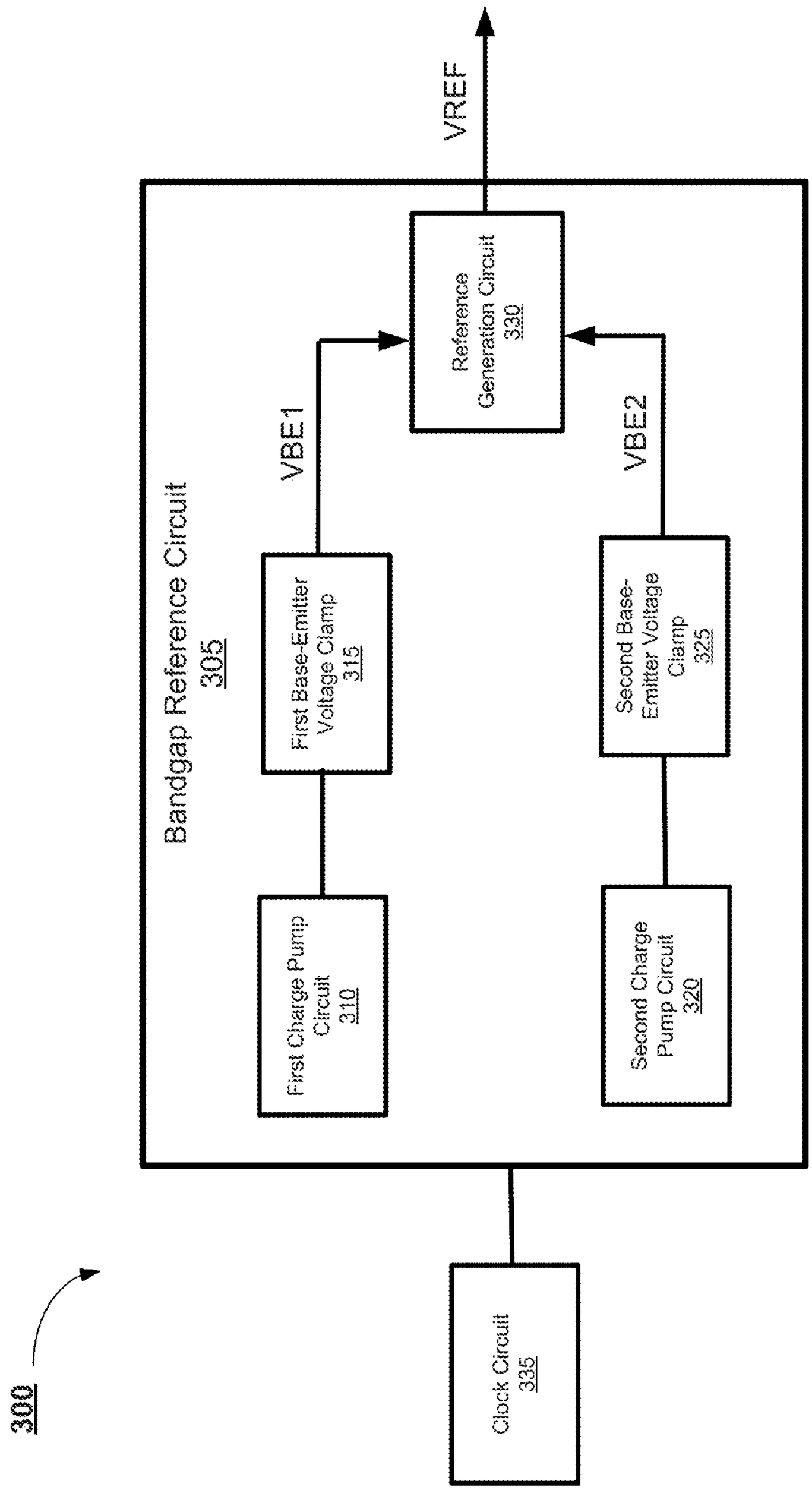

VREF
Reference Generation Circuit 330
VBE1
VBE2
Bandgap Reference Circuit 305
First Base-Emitter Voltage Clamp 315
Second Base-Emitter Voltage Clamp 325
First Charge Pump Circuit 310
Second Charge Pump Circuit 320
Clock Circuit 335
300

FIG. 3

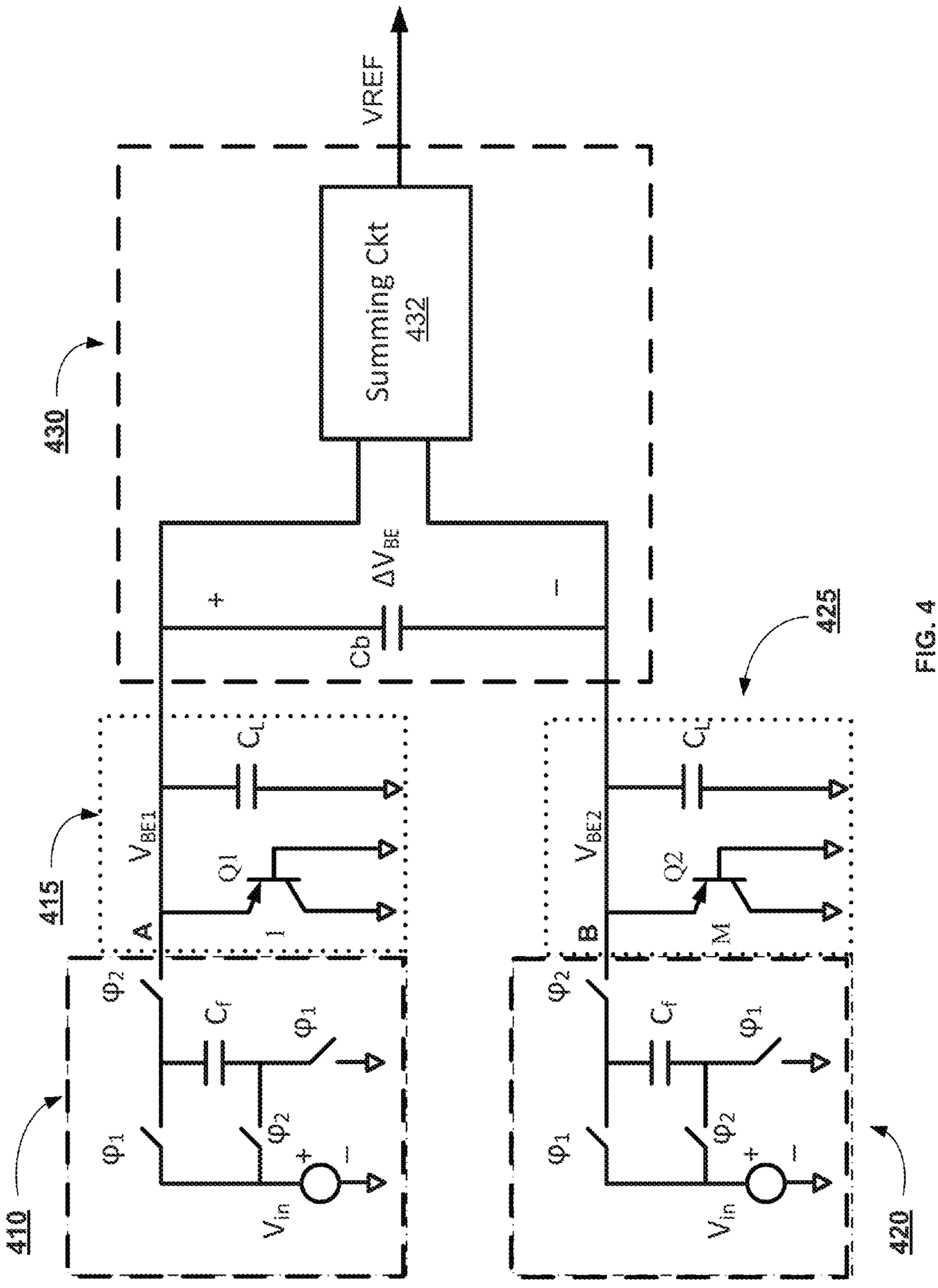

405
410
415
420
425
430
VREF
Summing Ckt
432
ΔV_{BE}
+
−
Cb
C_L
V_{BE1}
Q1
1
A
C_f
φ_2
φ_1
V_{in}
V_{BE2}
Q2
M
B

FIG. 4

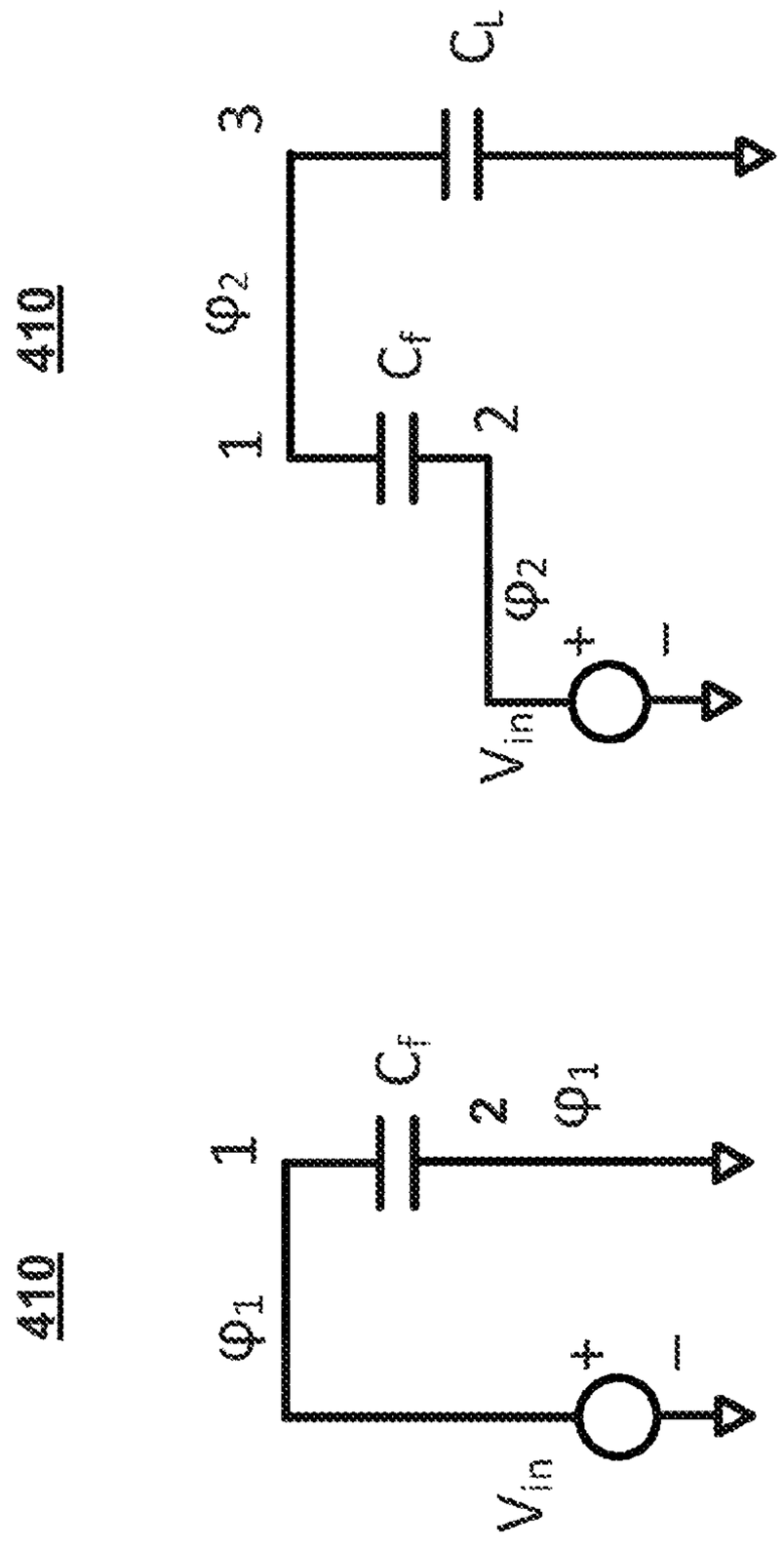


FIG. 5C

FIG. 5B

FIG. 5A

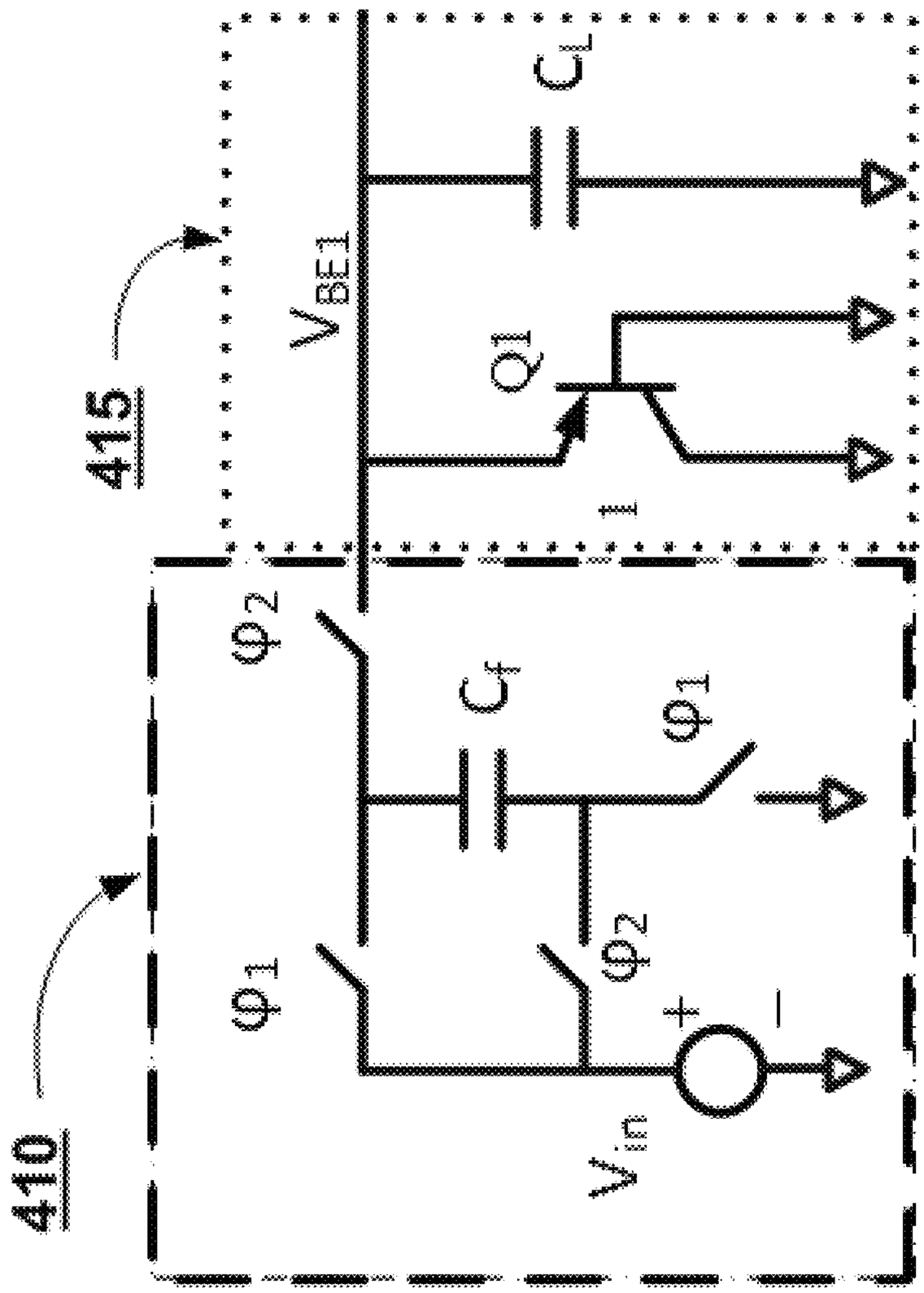


FIG. 6

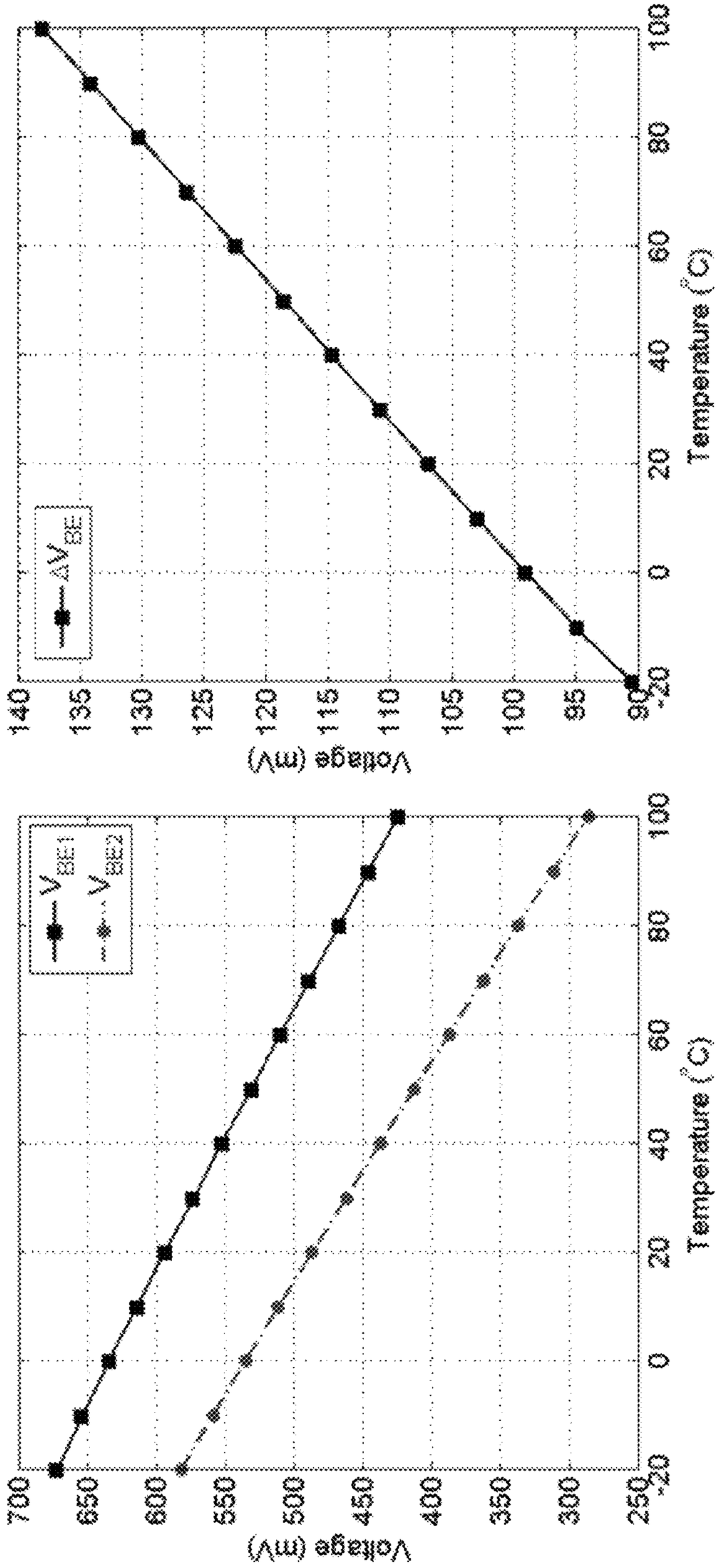

ΔV_{BE}
Voltage (mV)
140
135
130
125
120
115
110
105
100
95
90
-20
0
20
40
60
80
100
Temperature (°C)

FIG. 7B

V_{BE1}
V_{BE2}
Voltage (mV)
700
650
600
550
500
450
400
350
300
250
-20
0
20
40
60
80
100
Temperature (°C)

FIG. 7A

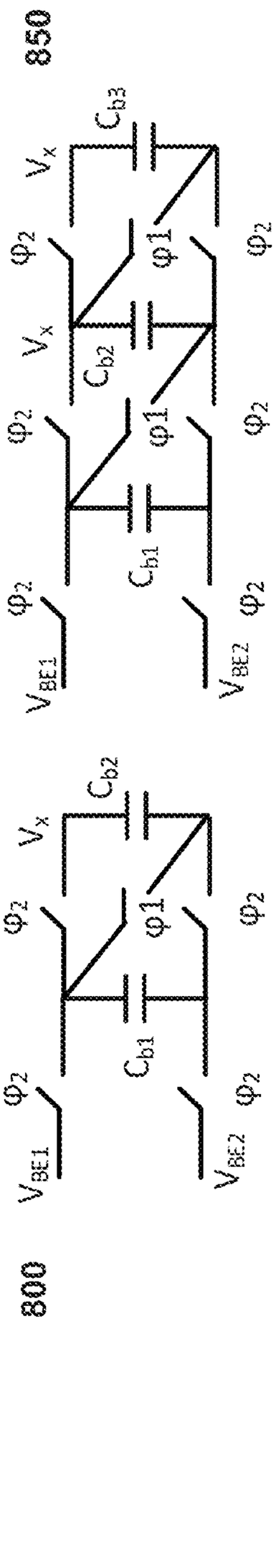


FIG. 8A

FIG. 8B

FIG. 8C

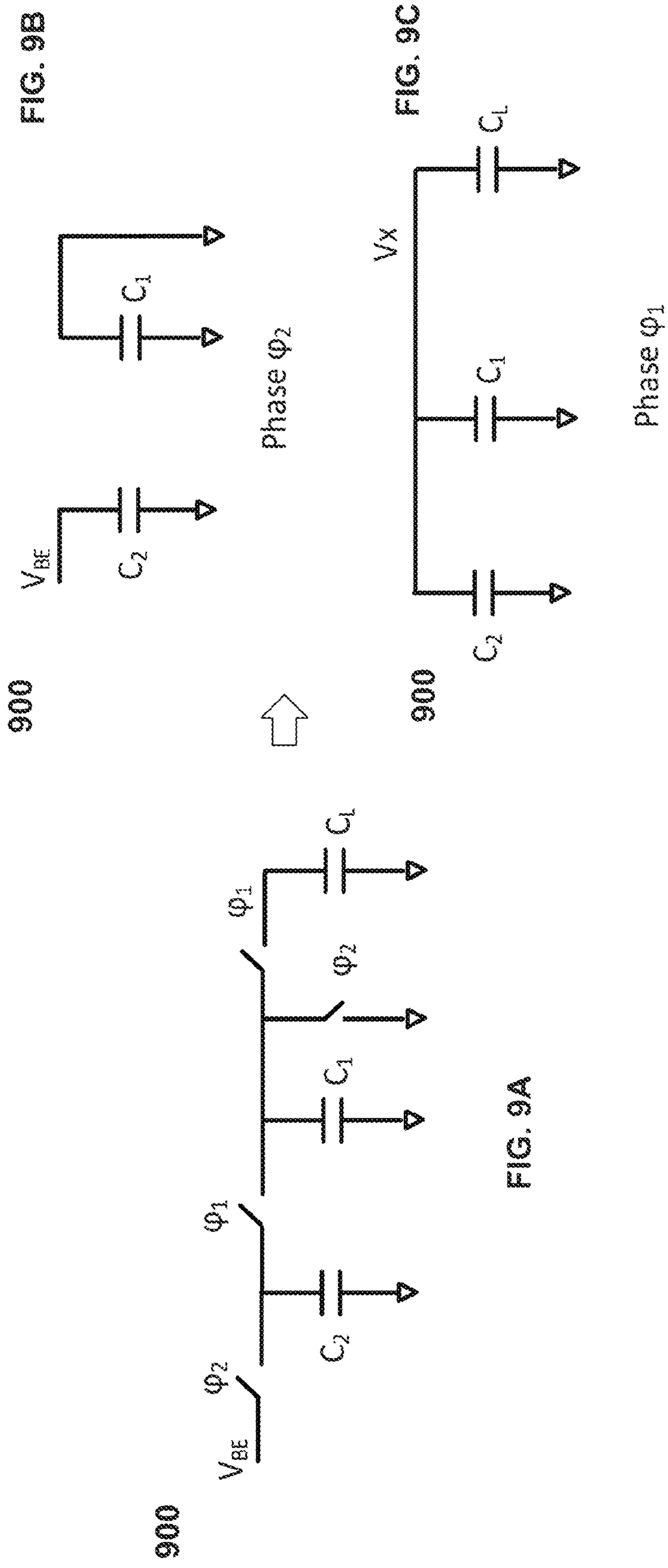


FIG. 9B

FIG. 9C

FIG. 9A

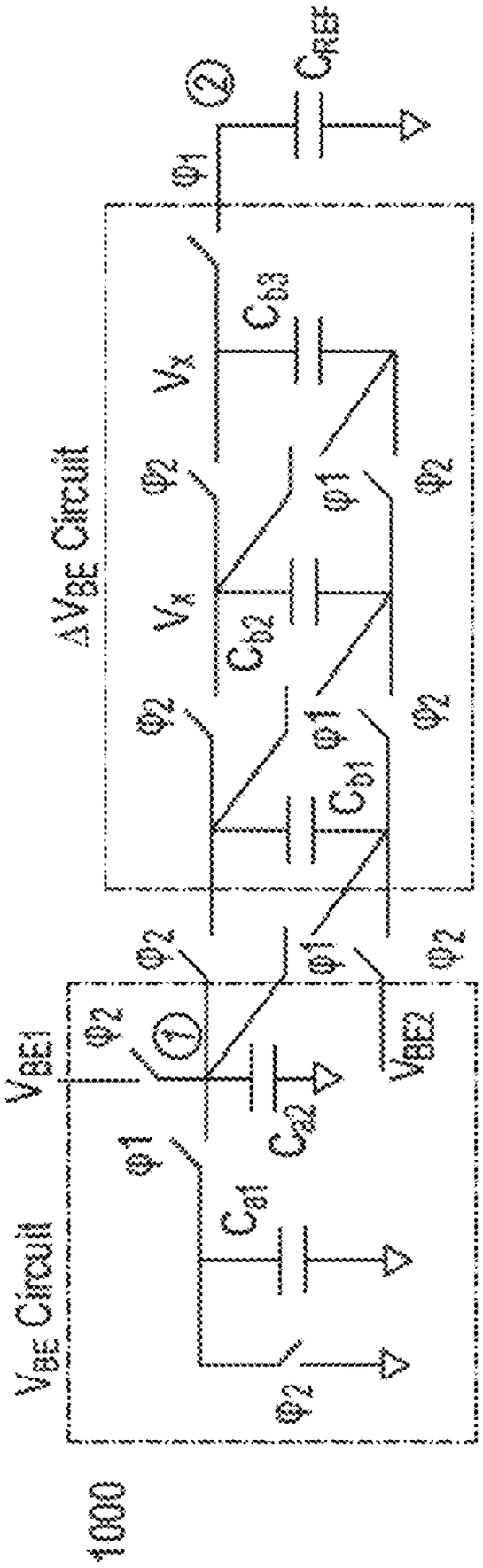


FIG. 10A

FIG. 10B

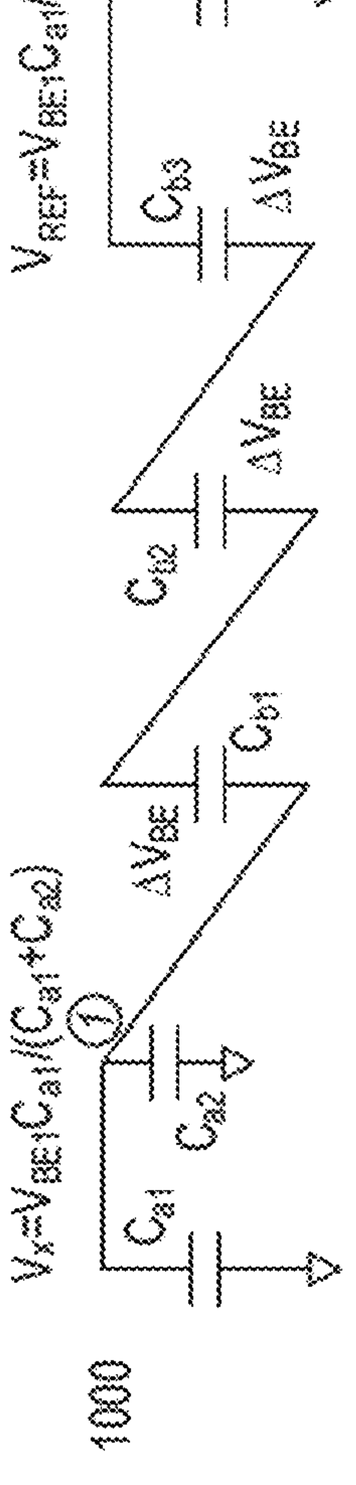


FIG. 10C

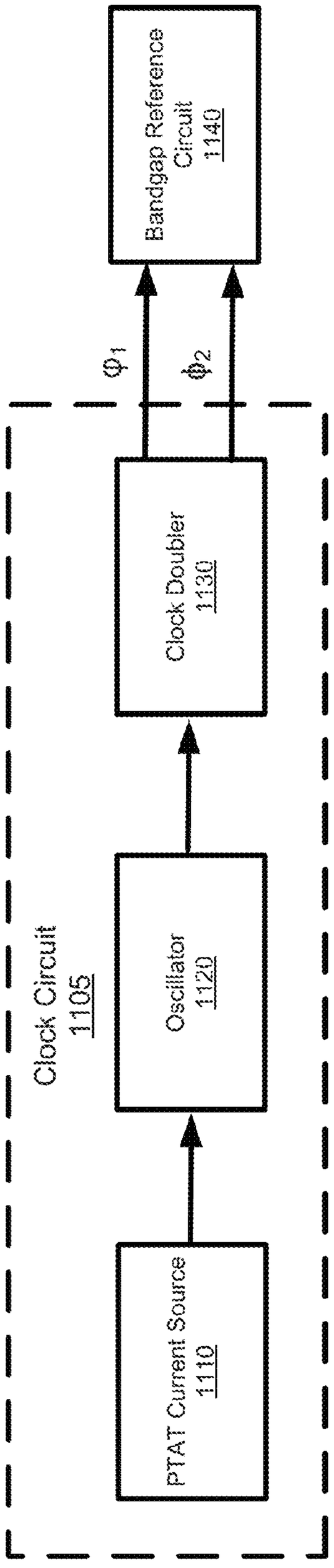

Bandgap Reference Circuit 1140
ϕ_1
ϕ_2
Clock Doubler 1130
Oscillator 1120
Clock Circuit 1105
PTAT Current Source 1110

FIG. 11

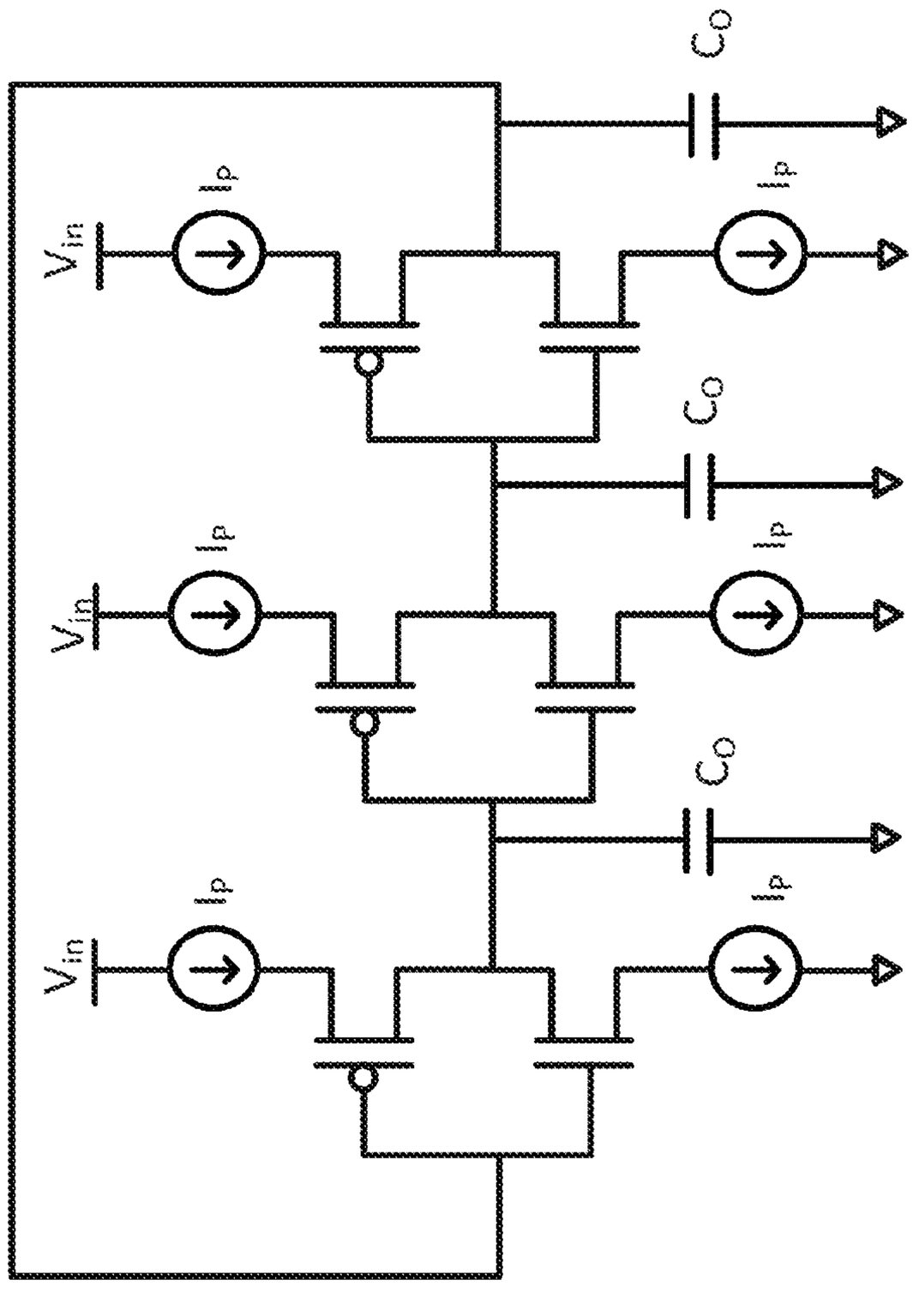


FIG. 12

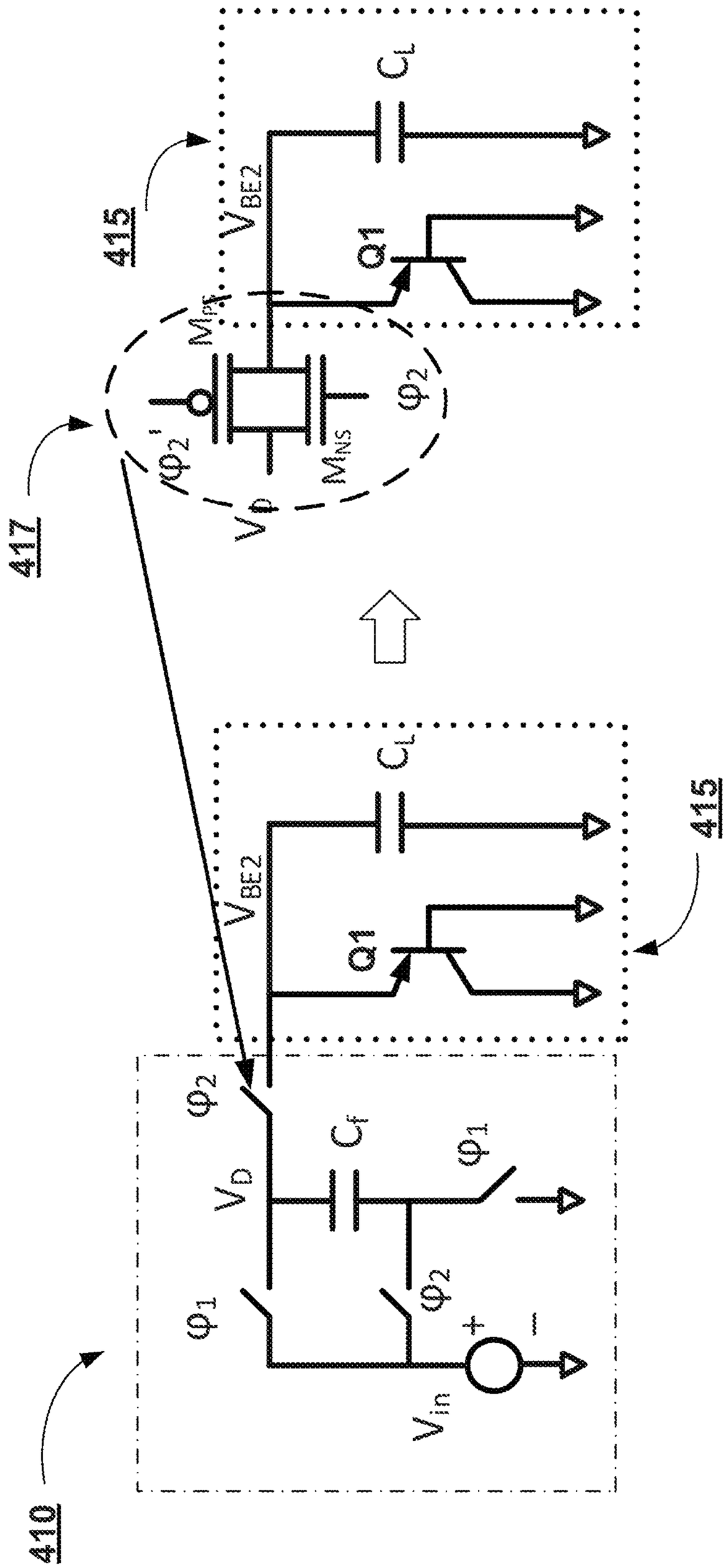


FIG. 13A

FIG. 13B

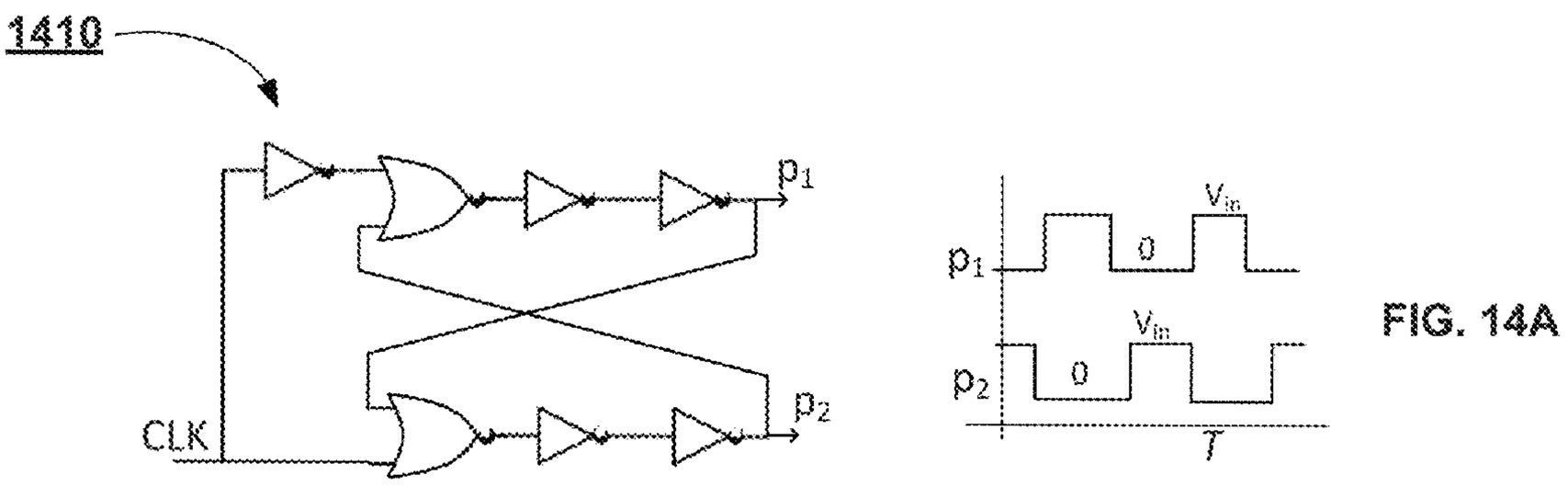
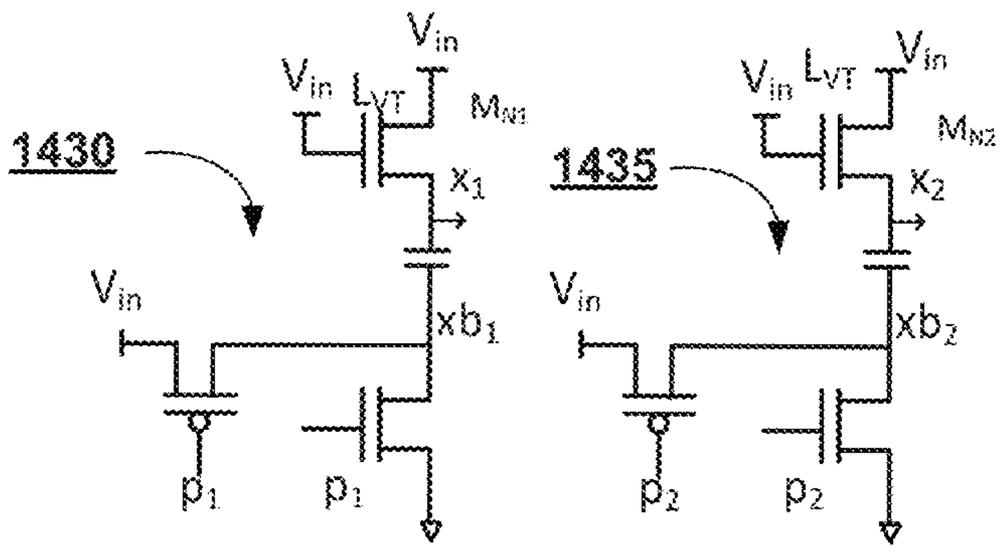


FIG. 14A



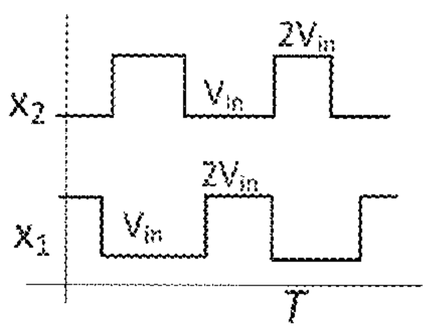


FIG. 14B

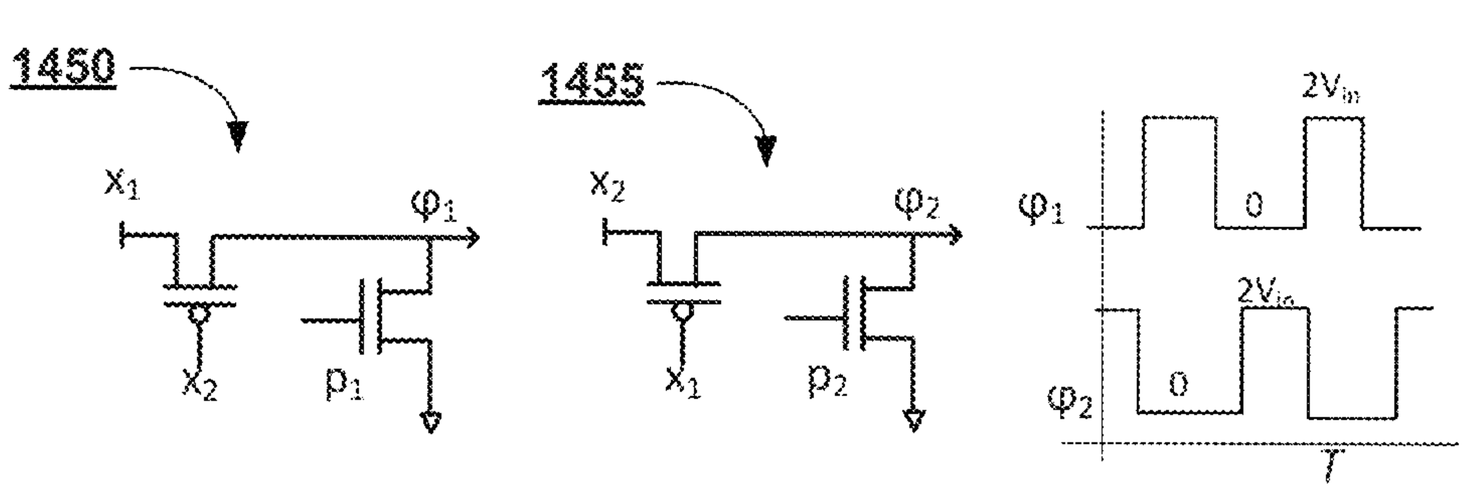


FIG. 14C

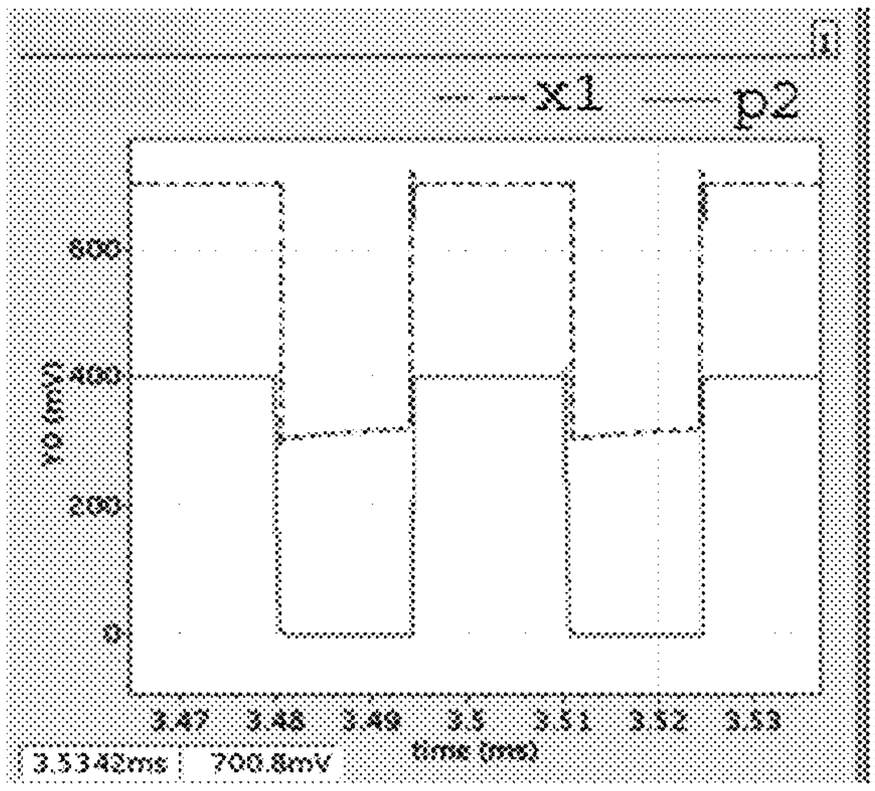


FIG. 15A

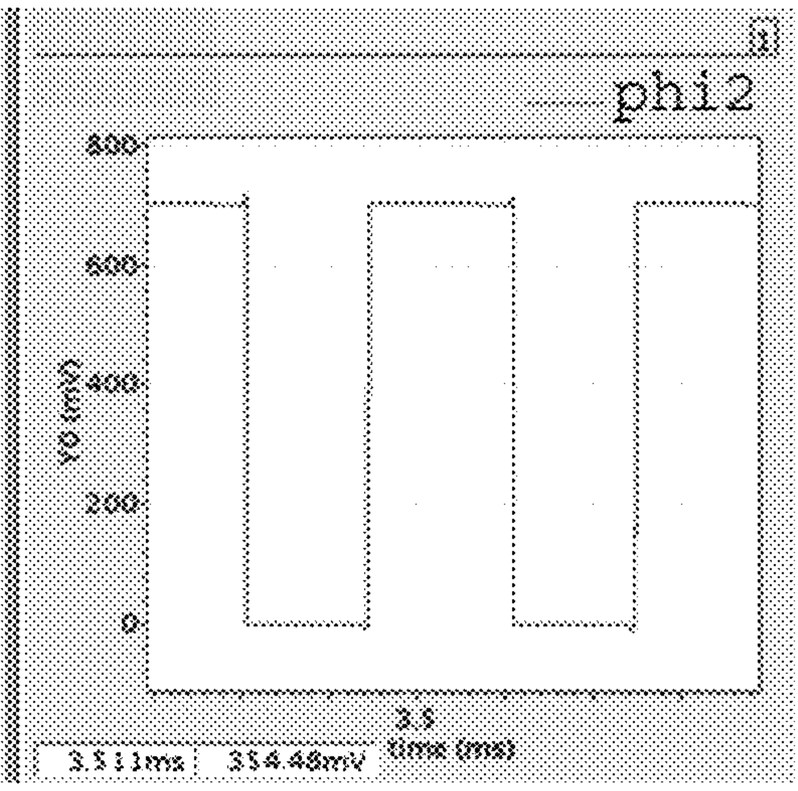


FIG. 15B

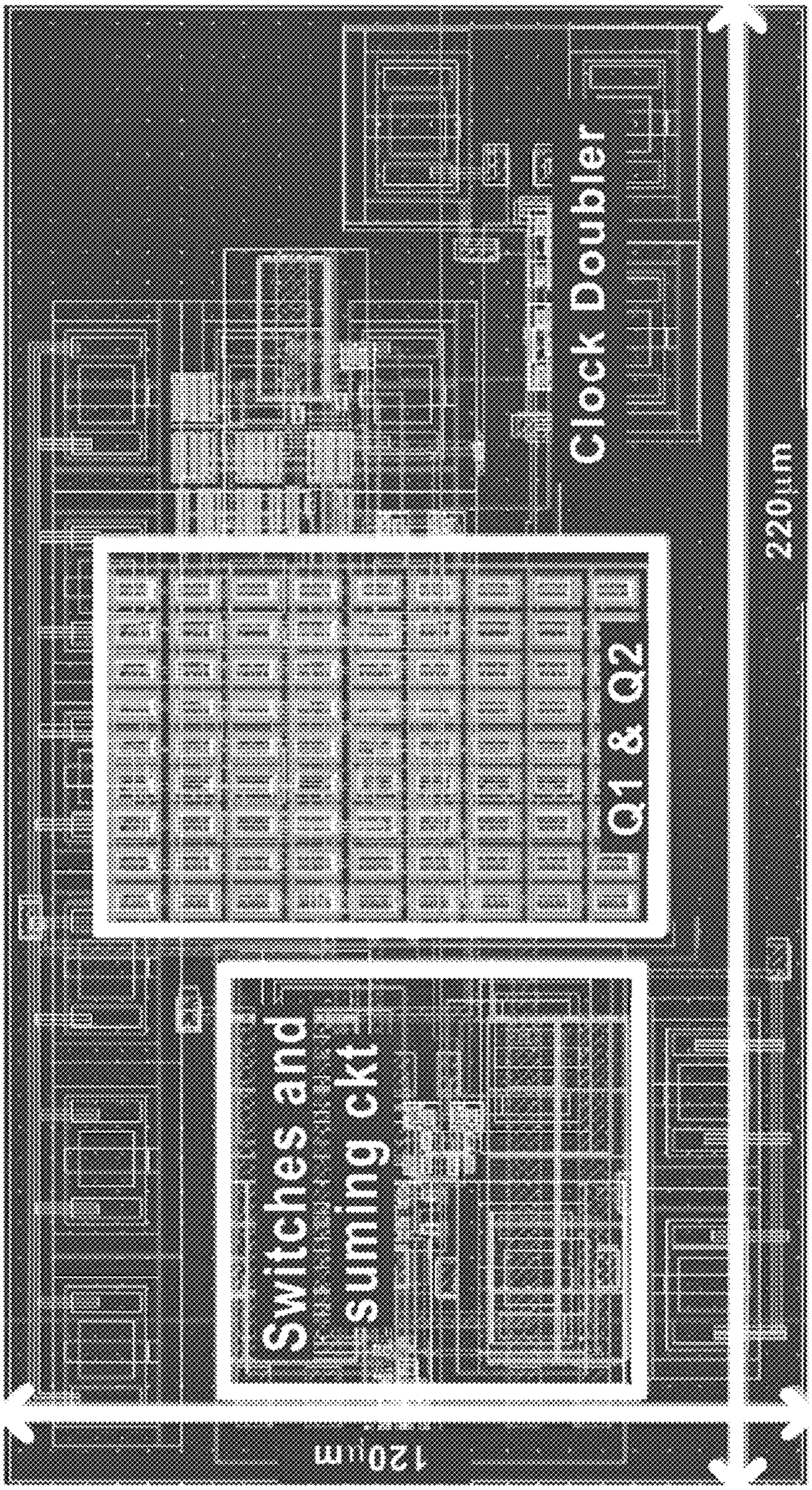


FIG. 16

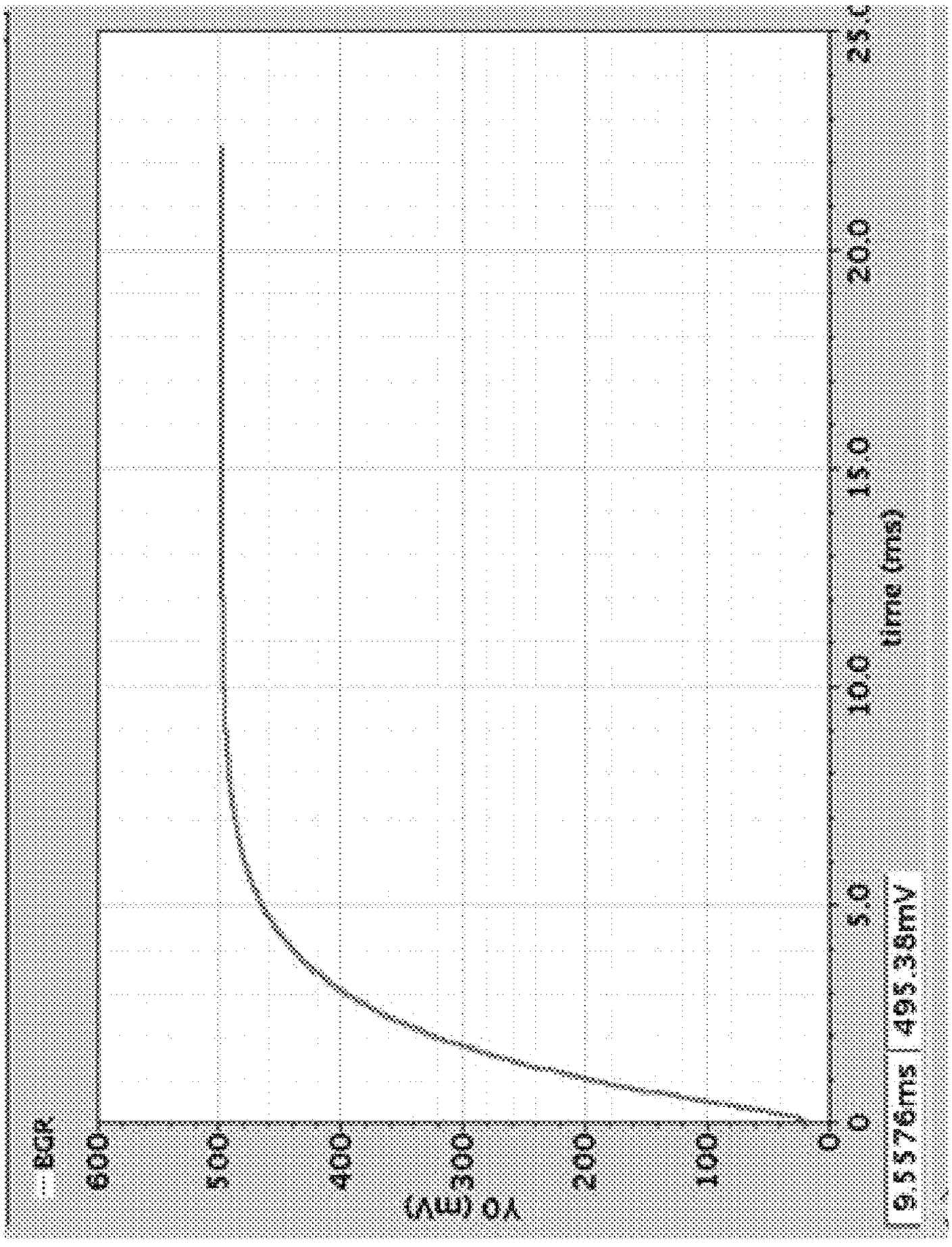

EGR
Yo (mV)
600
500
400
300
200
100
0
0
5.0
10.0
15.0
20.0
time (ms)
9.5579ms | 493.38mV

FIG. 17

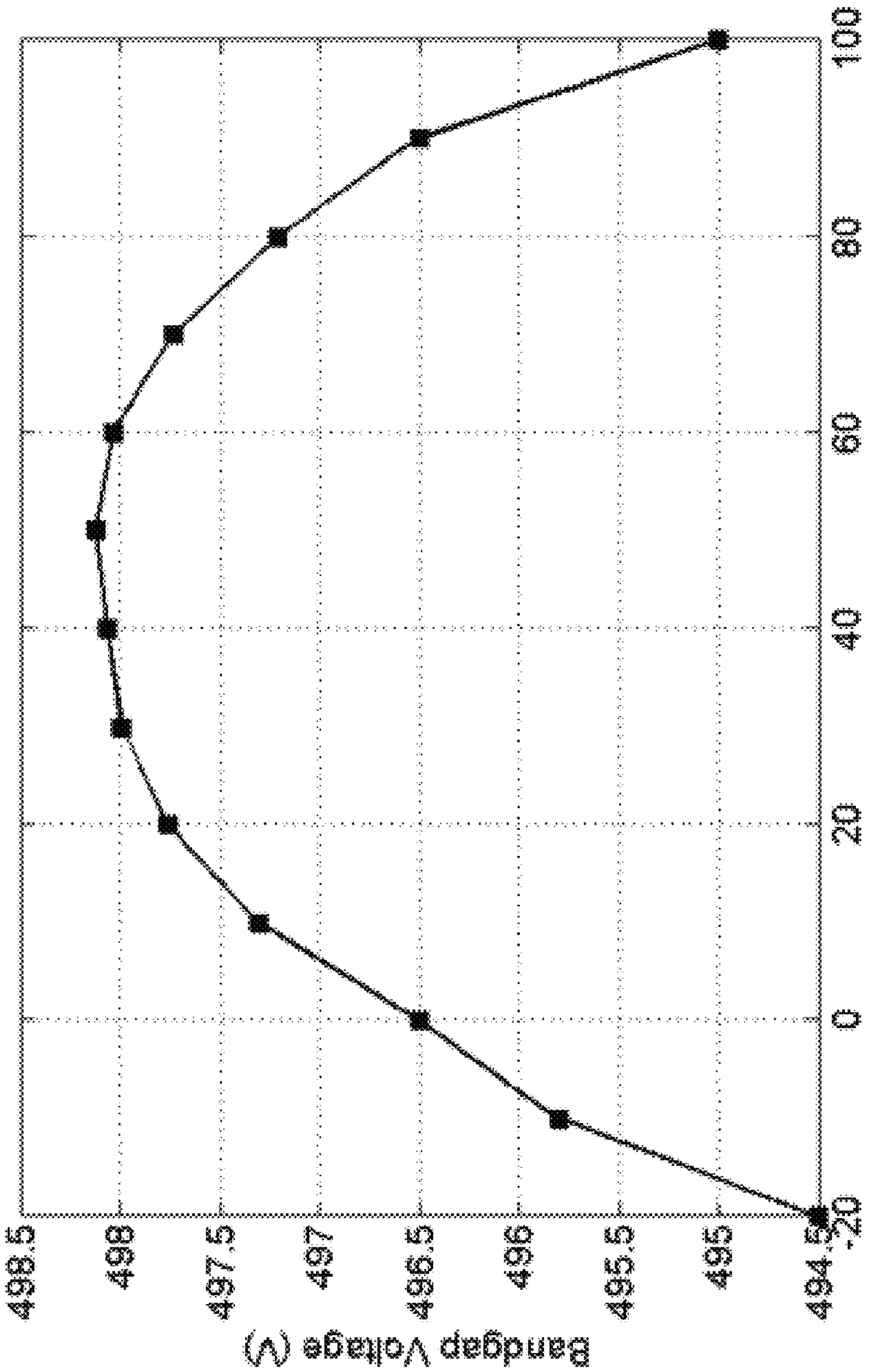

Bandgap Voltage (V)
498.5
498
497.5
497
496.5
496
495.5
495
494.5
-20
0
20
40
60
80
100
Temperature (°C)

FIG. 18

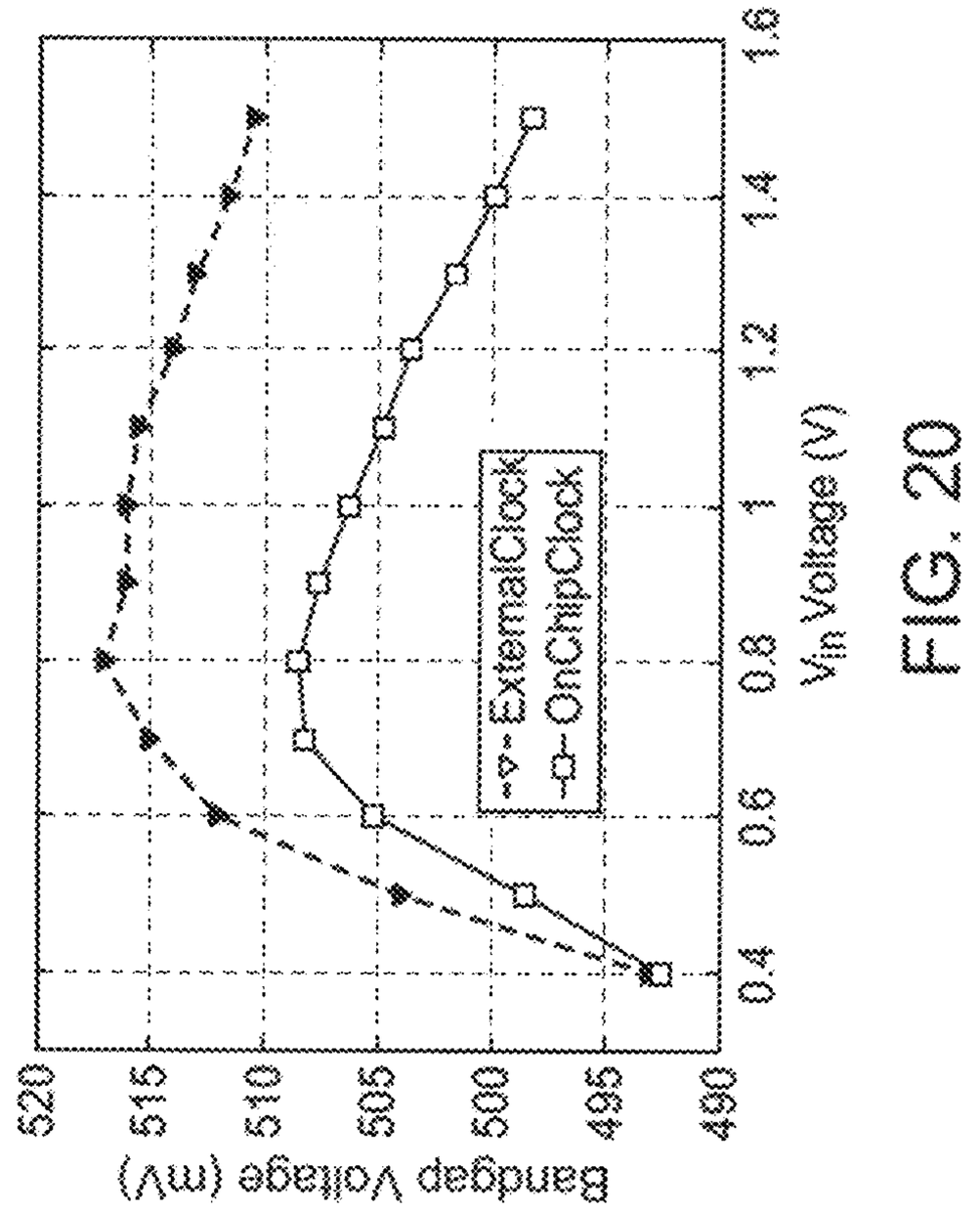

Bandgap Voltage (mV)
620
515
510
505
500
495
490
0.4
0.6
0.8
1
1.2
1.4
1.6
Vin Voltage (V)
External Clock
OnChip Clock

FIG. 20

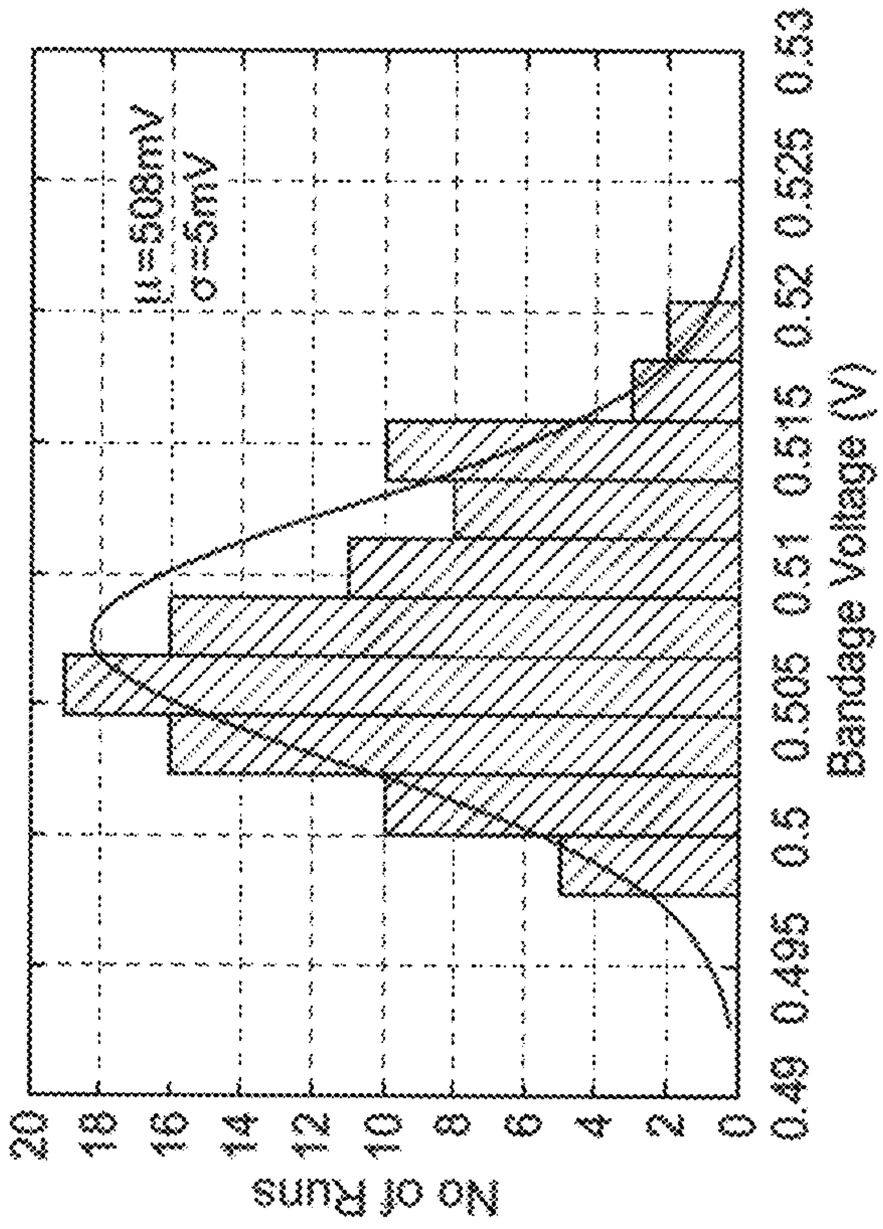

μ=508mV
σ=5mV
No of Runs
20
18
16
14
12
10
8
6
4
2
0
0.49
0.495
0.5
0.505
0.51
0.515
0.52
0.525
0.53
Bandage Voltage (V)

FIG. 19

METHODS AND APPARATUS FOR LOW INPUT VOLTAGE BANDGAP REFERENCE ARCHITECTURE AND CIRCUITS

CROSS REFERENCE TO RELATED APPLICATION

This application is a continuation of U.S. patent application Ser. No. 14/454,342, entitled "Methods and Apparatus for Low Input Voltage Bandgap Reference Architecture and Circuits," filed Aug. 7, 2014 (now U.S. Pat. No. 9,158,320), which is incorporated herein by reference in its entirety.

This application is also continuation of International Patent Application No. PCT/US15/43986, entitled "Methods and Apparatus for Low Input Voltage Bandgap Reference Architecture and Circuits," filed Aug. 6, 2015, which is incorporated herein by reference in its entirety.

BACKGROUND

Some embodiments described herein relate generally to methods and apparatus for generating a temperature insensitive bandgap voltage reference using an input (supply) voltage that is lower than the base-emitter voltage (V_{BE}) of a bipolar junction transistor (BJT).

Portable electronic/electrical systems that operate from a battery and/or from power harvested from the internal local environment typically consume small amounts of energy to prolong the system lifetime for a given amount of available energy. The energy budget for a portable system affects a widening set of applications due to a combination of requirements for smaller size (less battery volume, and hence less energy available), longer lifetimes (energy has to last longer), and/or more functionality (increased number of applications to implement with the same amount of energy). Many sensing applications use integrated circuits (ICs) or systems on chip (SoCs) to perform the sensing, computation, and communication functions that are used by a variety of applications.

In many cases, the time between sensor measurements can be relatively long such that the IC or SoC spends a substantial fraction of its lifetime in a standby mode. Known techniques reduce power consumed by the IC or SoC during standby mode, for example, by power gating unused circuit blocks. A subset of circuit blocks remains powered up during all times of device operation including, for example, a DC-DC regulator remains powered up to supply a stable operating voltage, V_{DD}, which in turn involves a voltage reference to set the correct value for V_{DD}. Typically, the most commonly used voltage reference is a bandgap reference that uses the silicon bandgap voltage to generate a temperature independent voltage reference.

An ideal voltage reference is independent of variation of power supply or temperature. A voltage reference is often included in many circuits, such as analog-to-digital converters, DC-DC converters, energy harvesting circuits, timing generation circuits, or other voltage regulators. Known implementations of bandgap reference typically involve the use of bipolar junction transistors (BJT) and large resistors to provide generate the bandgap voltage reference. Known conventional bandgap reference circuits, however, are limited to using input voltages higher than the base-emitter voltage (V_{BE}) of a BJT because they inject a current into the BJT using a current source, current mirror, resistor, or switched capacitor network at a voltage higher than V_{BE}.

Accordingly, for severely energy constrained electronic/electrical systems, a need exists for bandgap reference circuits with a low input voltage to allow for compatibility with energy harvesting and sub-threshold digital logic voltage levels. Additionally, a need exists to minimize power consumption for the bandgap reference circuit.

SUMMARY

In some embodiments, an apparatus includes a bandgap reference circuit having a first bipolar junction transistor (BJT) that can receive a current from a node having a terminal voltage and can output a base emitter voltage. The terminal voltage of the first BJT substantially corresponds to or is lower than the base emitter voltage of the first BJT for at least a time period. In such embodiments, the apparatus also includes a second bipolar junction transistor (BJT) having a device width greater than a device width of the first BJT. The second BJT can receive a current from a node having a terminal voltage and output a base emitter voltage, where the terminal voltage of the second BJT substantially corresponds to or is lower than the base emitter voltage of the second BJT for at least a time period. In such embodiments, the apparatus also includes a reference generation circuit operatively coupled to the first BJT and the second BJT, where the reference generation circuit can generate a bandgap reference voltage based on the base emitter voltage of the first BJT and the base emitter voltage of the second BJT.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. **1** is a block diagram of an integrated system used for feeding an input voltage to a bandgap reference circuit used in known portable electrical systems.

FIG. **2** is a schematic diagram representing a bandgap reference circuit generating a constant voltage reference across varying temperatures, according to an embodiment.

FIG. **3** is a schematic illustration of a bandgap reference circuit system that uses an input voltage less than the base-emitter voltage of a bipolar junction transistor, according to an embodiment.

FIG. **4** is a schematic illustration of a bandgap reference circuit that uses switched capacitor charge pumps to drive an input voltage less than the base-emitter voltage of a bipolar junction transistor, according to an embodiment.

FIGS. **5**A-C are schematic illustrations showing the charging of a switched capacitor charge pump circuit associated with the bandgap reference circuit shown in FIG. **4**.

FIG. **6** is a schematic illustration of the charged switched capacitor charge pump circuit shown in FIG. **5**A driving an input current into a base emitter voltage clamp.

FIGS. **7**A-**7**B present simulation results of the variation of V_{BE} and ΔV_{BE} as a function of temperature that is generated from the bandgap voltage reference circuit of FIG. **4**.

FIGS. **8**A-C are schematic illustrations of different scaling circuits to scale ΔV_{BE}, according to different embodiments.

FIGS. **9**A-C are schematic illustrations of different configurations of a scaling circuit to scale V_{BE}, according to an embodiment.

FIGS. **10**A-C are schematic illustrations of a reference generation circuit for generating the bandgap reference voltage, according to an embodiment.

FIG. **11** shows the block diagram of a clock signal generation scheme for the bandpass reference voltage circuit, according to an embodiment.

FIG. **12** is a schematic illustration of an oscillator shown in FIG. **11** that can be used to generate a clock signal for a bandgap reference circuit, according to an embodiment.

FIGS. **13**A-B are schematic illustrations of an implementation of switches for the bandgap reference circuit shown in FIG. **4**.

FIGS. **14**A-C are schematic illustrations of the steps involved in implementing a clock doubling technique to generate clock signals at different phases, according to an embodiment.

FIGS. **15**A-B present the results of simulations of an example of a clock doubler circuit that sends boosted clock phase signals to a bandgap voltage reference circuit.

FIG. **16** shows the annotated lay out of a bandgap reference circuit, according to an embodiment.

FIG. **17** is a graphical display of an example of the transient behavior of a bandgap reference circuit at startup.

FIG. **18** shows the simulated variation of an embodiment of a bandgap reference circuit output for a temperature range of −20° C. to 100° C.

FIG. **19** presents the results of a Monte-Carlo simulation that shows an example of the change in bandgap reference output with respect to process and mismatch variation.

FIG. **20** presents the results of a simulation that shows an example of the change in bandgap reference voltage with respect to variation with input voltage (V_{in}).

DETAILED DESCRIPTION

In some embodiments, an apparatus includes a bandgap reference circuit having a first bipolar junction transistor (BJT) that can receive a current from a node having a terminal voltage and can output a base emitter voltage. The terminal voltage of the first BJT substantially corresponds to or is lower than the base emitter voltage of the first BJT for at least a time period. In such embodiments, the apparatus also includes a second bipolar junction transistor (BJT) having a device width greater than a device width of the first BJT. The second BJT can receive a current from a node having a terminal voltage and output a base emitter voltage, where the terminal voltage of the second BJT substantially corresponds to or is lower than the base emitter voltage of the second BJT for at least a time period. In such embodiments, the apparatus also includes a reference generation circuit operatively coupled to the first BJT and the second BJT, where the reference generation circuit can generate a bandgap reference voltage based on the base emitter voltage of the first BJT and the base emitter voltage of the second BJT.

In some embodiments, an apparatus includes a base emitter voltage generation circuit having a bipolar junction transistor (BJT) configured to receive, in a voltage clamp configuration, a current from charge pump circuit and at a node having an input voltage and to output a base emitter voltage, where the input voltage substantially corresponds to or is lower than the base emitter voltage.

In some embodiments, an apparatus includes a clock circuit that is operatively coupled to a bandgap reference circuit, where the clock circuit has a first circuit portion that can receive from an on-chip clock a clock signal having an input voltage. The first circuit portion can produce (1) a first clock phase signal having a minimal voltage and a maximum voltage, and (2) a second clock phase signal non-overlapping with the first clock phase signal and having a minimal voltage and a maximum voltage. In such embodiments, the clock circuit also has a second circuit portion that is operatively coupled to the first circuit portion, where the second circuit portion includes a set of capacitors and a set of invertors that can collectively output a third clock phase signal and a fourth clock phase signal, the third clock phase signal and the fourth clock phase signal each having a minimal voltage greater than the minimum voltage of the first clock phase signal and the minimal voltage of the second clock phase signal. The third clock phase signal and the fourth clock phase signal each also has a maximum voltage greater than the maximum voltage of the first clock phase signal and the maximum voltage of the second clock phase signal. In such embodiments, the clock circuit also has a third circuit portion operatively coupled to the second circuit portion, where the third circuit portion includes a set of transistors that can output a fifth clock phase signal and a sixth clock phase signal. The fifth clock phase signal and the sixth clock phase signal each has a minimal voltage substantially equal to the minimum voltage of the first clock phase signal and the minimal voltage of the second clock phase signal. The fifth clock phase signal and the sixth clock phase signal each also has a maximum voltage substantially equal to the maximum voltage of the fourth clock phase signal and the maximum voltage of the fifth clock phase signal.

As used in this specification, the singular forms "a," "an" and "the" include plural referents unless the context clearly dictates otherwise. Thus, for example, the term "a transistor" is intended to mean a single transistor or a combination of transistors.

FIG. **1** is a block diagram of an integrated system used for feeding an input voltage to a bandgap reference circuit used in known portable electrical systems. The integrated system **100** is typically associated with larger electrical systems and, for example, can obtain energy from an external energy source **110** (e.g., a battery) using any number of energy harvesting mechanisms and in some instances, a boost converter **120**. The boost converter **120** typically enhances or boosts the voltage obtained from the energy harvesting source **110** to a value above V_{BE}. This can further be stabilized by the DC-DC regulator **130** before being sent to the bandgap reference circuit **140**. Typical known bandgap reference circuits such as the bandgap reference circuit **140** are limited to using input voltages higher than V_{BE} of a BJT because such known bandgap reference circuits inject a current into the BJT using a current source, current mirror, resistor, or switched capacitor network at a voltage higher than V_{BE}. Achieving a lower operational output voltage from the bandgap reference circuit **140**, however, is desirable for ultra-low-power (ULP) devices that include complex ICs, SoCs, body sensor nodes (BSNs) and wireless sensors for the internet of things. The output voltage from the bandgap reference circuit **140** determines the voltage at which the ULP device can turn on and operate because the reference voltage is used to turn on the power supplies of the ULP device. A lower bandgap reference voltage will reduce the turn-on voltage for the ULP device, reduce power loss, and increase the operational lifetime of the ULP device. Additionally, a lower bandgap reference voltage can also assist in the miniaturization of ULP devices.

FIG. **2** is a schematic diagram representing a bandgap reference circuit generating a constant voltage reference across varying temperatures, according to an embodiment. The bandgap reference circuit **200** includes a BJT base emitter voltage (V_{BE}) generated by a complementary-to-absolute-temperature (CTAT) voltage generation circuit **205**. The CTAT voltage generation circuit **205** includes a BJT (not shown in FIG. **2**) connected to a power source (not shown in FIG. **2**) in a diode configuration. The CTAT voltage

corresponds to the V_{BE} of the BJT transistor. The value of V_{BE} decreases with increasing temperature because of the generation of increased number of carrier with increased temperature. Because the number of carriers increases with temperature, the conductivity of the transistor (i.e., BJT) increases, thus decreasing the value of V_{BE}. In the example of FIG. **2**, the V_{BE} decreases with increasing temperature with a slope given by −2.2 mV/° C. The voltage V_t is the output of the proportional-to-absolute-temperature (PTAT) voltage generation circuit **210**. Unlike the CTAT voltage generation circuit **205**, here the output voltage increases in magnitude with increasing temperature. In the example of FIG. **2**, the voltage V_t increases with increasing temperature with a slope given by 0.085 mV/° C. The voltage V_t is multiplied with a constant K at the multiplier **215** and added to the CTAT voltage (V_{BE}) at the adder **220** to generate the bandgap reference voltage V_{REF} (where $V_{REF}=V_{BE}+KV_t$) that is temperature independent. The value of the constant K at the multiplier **215** is chosen such that the temperature dependence of the CTAT portion and PTAT portion of the bandgap reference circuit **200** cancel each other and V_{REF} becomes a temperature independent voltage reference (typically in the range of less than 10 ppm/° C.).

FIG. **3** is a schematic illustration of a bandgap reference circuit system that uses an input voltage less than the base-emitter voltage of a bipolar junction transistor. The bandgap reference circuit system **300** includes a bandgap reference circuit **305** operably coupled to a clock circuit **335**. The bandgap reference circuit **305** includes a first charge pump circuit **310**, a second charge pump circuit **320**, a first base-emitter voltage clamp **315**, a second base-emitter voltage clamp **325**, and a reference generation circuit **330**. It is to be noted that the BJT in the second base-emitter voltage clamp **325** has a device width greater than the device width of the BJT in the first base-emitter voltage clamp **315**. The bandgap reference circuit system **300** can generate a temperature insensitive bandgap reference voltage (V_{REF}) using an input (supply) voltage that is lower than the base-emitter voltage (V_{BE}) of a BJT. In such instances, the first charge pump circuit **310** (e.g., a boost circuit such as a switched capacitor circuit) drives a current into the first base-emitter voltage clamp **315** (e.g., including a first bipolar junction transistor (BJT) connected in parallel to a first load capacitor) from a voltage that is lower than the V_{BE} of the BJT in the first base-emitter voltage clamp **315**. This causes the first base-emitter voltage clamp **315** to clamp its base-emitter voltage at V_{BE1}. Similarly, the second charge pump circuit **320** drives a current into the second base-emitter voltage clamp **325** (e.g., also including a second BJT connected in parallel to a second load capacitor) from a voltage that is lower than the V_{BE} of the BJT in the second base-emitter voltage clamp **325**. This causes the second base-emitter voltage clamp **325** to clamp its base-emitter voltage at a different voltage V_{BE2}. The reference generation circuit **330** can include, for example, a programmable switched capacitor circuit can generate a temperature insensitive bandgap reference voltage (V_{REF}) from V_{BE1} and ΔV_{BE} ($V_{BE1}-V_{BE2}$), which can be any fractional multiple of the silicon bandgap voltage. In some configurations, the reference generation circuit **330** can include a capacitor that can store the voltage ΔV_{BE}. In such configurations, the reference generation circuit **330** can also include a summing circuit that can generate various constants for V_{BE1} and ΔV_{BE}, which are then added to generate the desired temperature insensitive bandgap reference voltage (V_{REF}).

It is to be noted that the process of generating constants for V_{BE1} and ΔV_{BE} can be, for example, a time-gated process where clock phase signals with different time intervals (non-overlapping) are used to open and close various switches in charge pump circuits **310** and **320** and the reference generation circuit **330**. Such clock phases are defined by discrete clock signals that are sent by the clock circuit **335** that is operably coupled to the bandgap reference circuit **305**. The clock circuit **335** can provide clock signals of different frequencies from, for example, an on-chip oscillator, a crystal oscillator or any other clock source. Additionally, the clock circuit **335** also includes a clock doubler circuit that is used to double the swing of the output clock signal to enable switches that can pass at least a voltage level of V_{BE}. The clock circuit **335** will be discussed in greater detail below in relation to FIGS. **11-16**.

FIG. **4** is a schematic illustration of a bandgap reference circuit that uses switched capacitor charge pumps to drive an input voltage less than the base-emitter voltage of a bipolar junction transistor, according to an embodiment. The bandgap reference circuit **405** includes switched capacitor charge pumps **410** and **420** (that each include capacitors C_f), base-emitter voltage clamp **415** (that includes BJT transistor Q**1** and capacitor C_L), base-emitter voltage clamp **425** (that includes BJT transistor Q**2** and capacitor C_L), and the reference generation circuit **430** that includes the summing circuit **432** and the capacitor C_b that stores the voltage ΔV_{BE}. The switched capacitor charge pump **410** typically generates voltages from the source V_{in}. The output of the switched capacitor charge pump **410** is connected to the BJT Q**1**, which in turn clamps its output voltage to V_{BE1}. Similarly, the switched capacitor charge pump **420** also generates voltages from V_{in}. The output of the switched capacitor charge pump **420** is connected to the BJT Q**2**, which in turn clamps its output voltage to V_{BE2}. The use of the charge pumps **410** and **420** to drive current into the BJTs Q**1** and Q**2** enables low voltage operation of the bandgap reference circuit **405**. Additionally, the clock circuit (e.g., clock circuit **335** shown in FIG. **3**), which is used to supply the clock signals for the two clock phases ϕ_1 and ϕ_2 used in the operation of the switched capacitor charge pumps **410** and **420**, can be made to operate at lower frequencies and input voltage (V_{in}) to reduce power consumption. The lower V_{in} and the lower clock frequency for the switched capacitor charge pumps **410** and **420** enables lower power consumption when compared to known bandgap voltage reference generators. Each of the sub-components (e.g., the charge pumps **410** and **420** and the reference generator circuit **430**) of the bandgap reference circuit **405** shown in FIG. **4** is described below.

For the bandgap reference circuit **405** shown in FIG. **4**, in some instances, the first BJT Q**1** can receive a current from a node (marked as A) having a first terminal voltage and can output a first base-emitter voltage (V_{BE1}), where the first terminal voltage (i.e., voltage at node A) substantially corresponds to or is lower than V_{BE1}. In such instances, the second BJT Q**2** can receive a current from a node (marked as B) having a second terminal voltage and can output a second base-emitter voltage (V_{BE2}), where the second terminal voltage (i.e., voltage at node B) substantially corresponds to or is lower than V_{BE2}. Note that the second BJT Q**2** has a device width greater than the first BJT Q**1** (as seen by 1 representing Q**1** and M representing Q**2** in FIG. **4**, where M>1). Additionally, in such instances, the bandgap reference circuit **405** also includes a reference generation circuit **430** that is operatively coupled to the first BJT Q**1** and the second BJT Q**2**, where the reference generation circuit **430** can generate a bandgap reference voltage (V_{REF}) based

on the base emitter voltage of the first BJT Q1 (V_{BE1}) and the base emitter voltage of the second BJT Q2 (V_{BE2}).

In the configuration of the bandgap reference circuit **405** shown in FIG. **4**, the first BJT Q1 can receive the terminal voltage for the first BJT Q1 (at node A) from a supply (e.g., V_{in}) without generation of an intermediate voltage that is higher than the base emitter voltage of the first BJT Q1 (V_{BE1}). Similarly, the second BJT Q2 can receive the terminal voltage for the second BJT Q2 (at node B) from a supply (e.g., V_{in}) without generation of an intermediate voltage that is higher than the base emitter voltage of the second BJT Q2 (V_{BE2}). Note that the first BJT Q1 receives the current for the first BJT Q1 from the first charge pump circuit **410** via at least one capacitor C_f. Similarly, the second BJT Q2 receives the current for the second BJT Q2 from the second charge pump circuit **420** via at least one capacitor C_f.

Referring to FIGS. **3** and **4**, the first charge pump circuit **410** is operatively coupled to the first BJT Q1 and a clock circuit (e.g., clock circuit **335** in FIG. **3**). The first charge pump circuit **410** can receive an input voltage (V_{in}) and can output the terminal voltage of the first BJT Q1 at node A, where V_{in} is less than the terminal voltage at node A. Similarly, the second charge pump circuit **420** is operatively coupled to the second BJT Q2 and a clock circuit (e.g., clock circuit **335** in FIG. **3**). The second charge pump circuit **420** can receive an input voltage (V_{in}) and can output the terminal voltage of the second BJT Q2 at node B, where V_{in} is less than the terminal voltage at node B. Note that the frequency of the clock signal send by the clock circuit **335** varies inversely with the terminal voltage for the first BJT Q1 (i.e., voltage at node A).

The clock circuit **335** sends a clock signal having a first clock phase ϕ_1 and a second clock phase ϕ_2. The first charge pump circuit **410** has a first configuration when receiving the first clock phase ϕ_1 signal and a second configuration when receiving the second clock phase ϕ_2 signal (as discussed in greater detail in relation to FIGS. **5-6** below). The first charge pump circuit **410** can output the terminal voltage of the first BJT Q1 (i.e., voltage at node A) based on a charge stored at a first capacitor (C_f) during the first configuration and the second configuration of the first charge pump **410** (as discussed in greater detail in relation to FIGS. **5-6** below). Similarly, the first charge pump circuit **420** has a first configuration when receiving the first clock phase ϕ_1 signal and a second configuration when receiving the second clock phase ϕ_2 signal. The second charge pump circuit **420** can output the terminal voltage of the second BJT Q2 (i.e., voltage at node B) based on a charge stored at a first capacitor (C_f) during the first configuration and the second configuration of the first charge pump **420**.

FIGS. **5**A-C are schematic illustrations showing the charging of a switched capacitor charge pump circuit associated with the bandgap reference circuit shown in FIG. **4**. The switched capacitor charge pump **410** (also known as charge pump circuit) shown in FIGS. **4** and **5**A-C can boost the input voltage V_{in} by a factor of two (i.e., $2*V_{in}$) and can also be used to output a voltage value of lower than V_{in}. The unloaded charge pump circuit **410** shown in FIG. **5**A uses non-overlapping clock phases ϕ_1 and ϕ_2, respectively. During operation in clock phase ϕ_1 as shown in FIG. **5**B, node **1** is connected to V_{in}, and node **2** (shown in FIG. **5**B) is connected to ground, charging the top plate of the capacitor C_f to V_{in} and the bottom plate of the capacitor C_f to ground. During operation in clock phase ϕ_2 as shown in FIG. **5**C, node **2** is connected to V_{in} and node **1** to the output capacitor C_L. Because the top plate of the capacitor C_f was charged to V_{in} during clock phase ϕ_1, charging the bottom plate of capacitor C_f to V_{in} in clock phase ϕ_2 allows the voltage at node **1** to go to $2*V_{in}$ because the voltage across the capacitor C_f is V_{in}. The capacitor C_L eventually charges to a voltage of $2*V_{in}$ after a given number of switching cycles at startup. Hence, the unloaded charge pump circuit **410** shown in FIG. **5**A can generate a voltage that is twice the input voltage V_{in}.

FIG. **6** is a schematic illustration of the charged switched capacitor charge pump circuit shown in FIG. **5**A driving an input current into a base emitter voltage clamp. The output of the charged switched capacitor charge pump circuit **410** is connected to the BJT Q1 of the base emitter voltage clamp **415**. Note the similar charged switched capacitor charge pump circuit **420** can be used to drive the base emitter voltage clamp **425** that includes the BJT Q2 (that in the example of FIG. **4** is M times bigger than Q1). In the absence of the BJT transistor Q1, the output of the base emitter voltage clamp **415** would go to $2*V_{in}$. The presence of the BJT transistor Q1, however, restricts the output voltage of the base emitter voltage clamp **415** to V_{BE1}. A significant advantage of the circuit shown in FIG. **6** is that the voltage V_{in} involved in generating V_{BE1} is smaller than V_{BE} (where $V_{BE}=V_{BE1}$ for the case of transistor Q1 and $V_{BE}=V_{BE2}$ for the case of transistor Q2). The minimum voltage for the bandgap to be operational V_{min} is given by the following equation:

$$V_{min} > \frac{V_{BE}}{N} \tag{1}$$

Where N=2 is applicable for a voltage doubling switched capacitor charge pump as described in FIGS. **4-6**. Eq. 1 shows that in some other configurations, if a voltage tripler or a higher order (i.e., N) switched capacitor charge pump is used, even lower values of V_{in} can be obtained.

FIGS. **7**A-**7**B present simulation results of the variation of V_{BE} and ΔV_{BE} as a function of temperature that is generated from the bandgap voltage reference circuit of FIG. **4**. FIG. **7**A shows the temperature dependence of V_{BE1} and V_{BE2} where a CTAT behavior of both V_{BE1} and V_{BE2} with respect to temperature is observed. Conversely, FIG. **7**B shows the temperature dependence of ΔV_{BE} where a PTAT behavior of ΔV_{BE} with respect to temperature is observed. The voltages of V_{BE1}, V_{BE2} and ΔV_{BE} have been simulated using a V_{in} of 0.4V. The weights of the voltages V_{BE1} and ΔV_{BE} are added to generate the bandgap reference voltage. In some instances, the bandgap reference circuit shown in FIG. **4** can generate a bandgap reference voltage (V_{REF}) given by the following equation:

$$V_{REF}=a(V_{BE1}+b\Delta V_{BE}) \tag{2}$$

Where the constants a and b are involved in generating the weights for V_{BE} and ΔV_{BE} to generate V_{REF}. Note that in other instances, a different summing circuit (e.g., summing circuit **432** shown in FIG. **4**) using different values of V_{BE1}, V_{BE2} and ΔV_{BE} can generate a different value for V_{REF}. The constants a and b in Eq. 2 above are defined or established by employing switched capacitor circuit techniques as opposed to the use of resistors that are typically used in known methods. In such known methods, the use of resistors increases the area of the circuit for low power or ULP devices. The power consumption of the bandgap reference circuit typically depends on the value of the resistor with typically larger resistors leading to lower power consumption. For example, the size of resistors typically involved in the design of a 200 nW bandgap reference circuit is approxi-

mately 14 MΩ. Resistors in the MΩ-sized range typically occupy a large physical area, a feature undesirable for low power or ULP devices. Additionally, for low power applications, large resistors are used in known bandgap reference circuits and such large resistors also increase the thermal and flicker noise for the bandgap reference circuit. The use of switched capacitor circuits, however, can define or establish such constants (e.g., a and b as shown in Eq. 2) with a significantly lower area.

The different voltage parameters described above (e.g., V_{BE1}, V_{BE2} and ΔV_{BE}) can be scalable, particularly for dynamic voltage scaling (DVS) applications. The bandgap reference voltage V_{REF} discussed in Eq. 2 is also scalable where a and b are the constants used to produce a scalable bandgap reference voltage. In Eq. 2, one of the constants can be a natural number while the other constant a rational number. Note that the circuits used for physically scaling the different voltages V_{BE1}, V_{BE2} and ΔV_{BE} are included within the summing circuit (e.g., summing circuit **432** shown in FIG. **4**) of the reference generation circuit.

FIGS. **8**A-C are schematic illustrations of different scaling circuits to scale ΔV_{BE}, according to different embodiments. As seen in FIG. **8**A, the capacitor C_b is connected between the nodes with the voltage of V_{BE1} and V_{BE2}, respectively, that are generated from the switched capacitor charge pump based bandgap reference circuit as shown in FIG. **4** (i.e., voltage across capacitor C_b is ΔV_{BE}). For generating different bandgap reference voltages (V_{REF}), ΔV_{BE} has to be multiplied (or scaled) by different constants. The scaling circuits **800** presented in FIGS. **8**A-C present ways to generate three alternate constants for ΔV_{BE}, namely one (FIG. **8**A), two (FIG. **8**B) and three (FIG. **8**C). FIG. **8**A shows the circuit for generating $1*\Delta V_{BE}$, which is simply the portion of the charge-pump-based bandgap reference circuit shown in FIG. **4** with no additional signal modifications performed by the reference generation circuit. FIG. **8**B shows the scaling circuit **800** for generating $2*\Delta V_{BE}$ that uses the two non-overlapping clock phases ϕ_1 and ϕ_2. In phase ϕ_2, the voltages V_{BE1} and V_{BE2} are connected across the capacitors C_{b1} and C_{b2}. In phase ϕ_1, the connection of the capacitors are re-arranged and the top plate of C_{b1} is connected to the bottom plate of C_{b2} are shown in FIG. **8**B. So the voltage appearing on the top plate of C_{b2} is $2*\Delta V_{BE}$. This is a depiction of the voltage doubling scheme. Similarly, FIG. **8**C shows the scaling circuit **850** for generating $3*\Delta V_{BE}$ that also uses the two non-overlapping clock phases ϕ_1 and ϕ_2. The functioning of the voltage tripling circuit **850** in FIG. **8**C is similar to the voltage doubling circuit **800** shown in FIG. **8**B. Note that varying the scaling circuit can allow scaling or multiplication of ΔV_{BE} by any integer value.

In some instances, the generation of multiple bandgap reference voltages can be involved for SoC applications to generate multiple V_{DDS} values. In such instances, a ΔV_{BE} voltage can be selected based on the transistor Q**2** as shown in FIG. **4**. Subsequently, multiple scaled values of ΔV_{BE} can be generated as described above. This can complete half of the scaling involved in generating the appropriate V_{REF} values according the Eq. 2. Subsequently, different fractional constant multipliers of V_{BE} also can be generated to obtain the appropriate bandgap reference voltages (V_{REF}) for the SoC applications.

FIGS. **9**A-C are schematic illustrations of different configurations of a scaling circuit to scale V_{BE}, according to an embodiment. Note that the scaling circuit **900** shown in FIGS. **9**A-C will scale or multiply V_{BE} with a fractional number (and not an integer). The scaling circuit **900** for V_{BE} also includes switched capacitor circuits with non-overlapping clock phases ϕ_1 and ϕ_2. FIG. **9**A shows the unloaded scaling circuit **900** for scaling V_{BE} before clock phase signals have been applied. During operation in clock phase ϕ_2 as shown in FIG. **9**B, the capacitor C_2 is connected to V_{BE}, while the capacitor C_1 is connected to ground. Therefore the charge stored on capacitor C_2 is given by:

$$Q_2 = V_{BE} C_2 \tag{3}$$

In contrast, the charge stored on the capacitor C_1 is zero. During operation in clock phase ϕ_1 as shown in FIG. **9**C, the capacitors C**1** and C**2** are connected together and so the total charge on the capacitors remains the same. Therefore:

$$Q_2 = Q_{vx} \tag{4}$$

So,

$$V_{BE} C_2 = V_{Xx}(C_1 + C_2) \tag{5}$$

Therefore V_x is given by:

$$V_X = V_{BE} \frac{C_2}{C_1 + C_2} \tag{6}$$

Hence, by selecting the appropriate values of the capacitors C_1 and C_2, a value of V_X is obtained that is a fraction of V_{BE} as given by Eq. 6. The discussion presented herein in relation to FIGS. **8**A-C and FIGS. **9**A-C relate to scaling the voltages V_{BE} and ΔV_{BE}, respectively. Next, adding the scaled voltages V_{BE} and ΔV_{BE} in the reference generation circuit to achieve the desired bandgap reference voltage value V_{REF} is discussed.

FIGS. **10**A-C are schematic illustrations of a reference generation circuit for generating the bandgap reference voltage, according to an embodiment. The reference generation circuit **1000** includes the circuits used for generating constants for V_{BE} and ΔV_{BE} as discussed in FIGS. **8**A-C and FIGS. **9**A-C and also uses the switched capacitor scheme to generate the desired bandgap reference voltage value V_{REF}. FIG. **10**A shows the reference generation circuit **1000** (or summing circuit) with the appropriate signals. During operation in clock phase ϕ_2, the switches connected with the (clock phase) signal ϕ_2 are closed and the reference generation circuit **1000** is configured as shown in FIG. **10**B. The capacitor C_{a1} is discharged to the ground while the top plate of the capacitors C_{a2}, C_{b1}, C_{b2}, and C_{b3} are connected to V_{BE1}. The bottom plate of the capacitor Ca**2** is connected to ground, while the bottom plate of C_{b1}, C_{b2}, and C_{b3} are connected to V_{BE2}. So, the voltage across C_{a2} is V_{BE1}, while the voltage across C_{b1}, C_{b2}, and C_{b3} is ΔV_{BE}. During operation in clock phase ϕ_1, the switches are reconfigured and the reference generation circuit **1000** is arranged as shown in FIG. **10**C. First, the capacitors C_{a1} and C_{a2} are connected and charge shared to generate the V_{BE} component of the bandgap reference voltage. The voltage at node **1** is given by:

$$V_1 = V_{BE1} \frac{C_{a2}}{C_{a1} + C_{a2}} \tag{7}$$

Additionally, during operation in clock phase ϕ_1, the capacitors C_{b1}, C_{b2}, and C_{b3} are rearranged to generate $3*\Delta V_{BE}$ between nodes **1** and **2** that leads to the generation of the desired bandgap reference voltage V_{REF} as shown by:

$$V_{REF} = V_{BE1}\frac{C_{a2}}{C_{a1}+C_{a2}} + 3\Delta V_{BE} \quad (8)$$

Equation 8 shown above shows the generation of the proposed temperature independent bandgap reference voltage. It is to be noted that other values of V_{REF} can be generated (or obtained) different values for the capacitors C_{a1} and C_{a2} and different scaling factors (or weights) for ΔV_{BE}.

The bandgap reference circuit described in FIGS. **1-10** uses switched capacitor circuits that use two non-overlapping phases of a clock signal having a first clock phase ϕ_1 and a second clock phase ϕ_2. The clock signal is generated by a clock circuit (e.g., clock circuit **335** shown in FIG. **3**) for the proper functioning of the bandgap reference circuit. The temperature independent bandgap reference voltage (V_{REF}) as described by Eq. 8 above is independent of clock frequency in the embodiments of the bandgap reference circuits presented in FIGS. **1-10**. Hence, the power consumption of the clock circuit used to achieve V_{REF} can be reduced or minimized by operating the clock circuit at a very low frequency. The frequency of the clock signal should, however, be high enough to maintain the bias voltage of BJT Q**1** (V_{BE1}) and BJT Q**2** (V_{BE2}) against leakage. Additionally, the frequency of the clock signal sent by the clock circuit varies inversely with the terminal voltage for the first BJT (e.g., Q**1** in FIG. **4**). Hence, a low frequency, low power clock circuit can be used to generate the desired temperature independent bandgap reference voltage (V_{REF}).

The different switches used in the bandgap reference circuits can pass a voltage equivalent to at least V_{BE}, which is a voltage higher than V_{in}. Therefore, the clock signals associated with clock phases ϕ_1 and ϕ_2 can sweep from 0 to $>V_{BE}$. If not, the voltage input at the gate terminal of a switch (e.g., an NMOS switch) is lower than the voltage value (or voltage level) that the switch has to pass, and the switch cannot pass the full voltage. Accordingly, because the switches in the bandgap reference circuit (e.g., switches in the summing circuit and the switched capacitor charge pumps) pass voltages up to V_{BE}, the clock signals (that drives the gate terminals of such switches) have voltages substantially equal to or higher than V_{BE}.

FIG. **11** shows the block diagram of a clock signal generation scheme for the bandpass reference voltage circuit, according to an embodiment. The clock circuit **1105** is operably coupled to a bandgap voltage reference circuit **1140**. The clock circuit **1105** includes an oscillator **1120** to provide the initial clock signal. The oscillator **1120** can be, for example, a current-controlled ring oscillator (e.g., that can produce clock signal of approximately 30 kHz at 0.4V V_{in} and consume approximately 2 nW of power). In other configurations, the initial clock signal can be generated by, for example, an on-chip oscillator, a crystal oscillator (that is an electronic oscillator circuit that uses the mechanical resonance of a vibrating crystal of piezoelectric material to define an electrical signal with a very precise frequency), or any other appropriate clock source. The clock circuit **1105** also includes a PTAT current source **1110** and a clock doubler **1130**. The PTAT current source **1110** can be the same source that supplies V_{in} for the bandgap voltage reference circuit **1140**. The clock doubler **1130** is used to double the voltage sweep range of the output clock signal to enable switches in the bandgap voltage reference circuit **1140** to pass at least a voltage level of V_{BE} as discussed above. It is to be noted that the output clock signals from the clock doubler **1130** occur in two non-overlapping clock phases ϕ_1 and ϕ_2.

FIG. **12** is a schematic illustration of an oscillator shown in FIG. **11** that can be used to generate a clock signal for a bandgap reference circuit, according to an embodiment. In the example of FIG. **12**, the oscillator is represented by a current-controlled ring oscillator circuit **1200**. Referring to FIGS. **11-12**, the current-controlled ring oscillator **1200** uses the current from the PTAT source **1110**. This current increases with temperature but does not change with V_{in}. Because the power consumption of the PTAT current source **1110** increases with increasing V_{in}, the architecture of the current-controlled ring oscillator **1200** is such that the frequency of the of the clock signals decreases with increasing V_{in} to keep the power consumption of the clock circuit **1105** low. This is because the delay of one inverter cell (T_{RO}) in the current-controlled ring oscillator is given by:

$$T_{R0} = \frac{C_0 V_{in}}{2I_0} \quad (9)$$

Therefore, the frequency of the ring oscillator is given by:

$$f_0 = \frac{1}{6T_{Ro}} = \frac{3I_0}{C_0 V_{in}} \quad (10)$$

Eq. (10) gives the expression of the output frequency (f_0) for the current controlled ring oscillator. The current I_0 used in Eq. 9 and 10 above comes from a PTAT current source (e.g., PTAT current source **1110** in FIG. **11**), which remains constant with V_{in} because of the high power supply rejection. Because the current I_p within the current-controlled ring oscillator remains constant with I_0, Eq. (10) shows the output frequency of the current controlled ring oscillator (f_0) decreases with increasing V_{in}, which helps keep the power consumption of the bandgap voltage reference circuit low with increasing V_{in}.

Note that the current-controlled clock source (implemented by using a ring oscillator and the PTAT current source) as described in FIGS. **11-12** is a satisfactory choice to cater to a widely varying V_{in} voltage to reduce or restrict power consumption. If, however, in some configurations, a clock source such as a crystal oscillator, a system clock, or a real time clock is already available on the device chip for other applications, then overall system power can be reduced by using such existing internal clock sources instead of generating a clock source for the bandgap voltage reference circuit as described above.

As described above, the clock circuit sends clock signals associated with clock phases ϕ_1 and ϕ_2 that sweep from 0V to a voltage greater than V_{BE} to pass a voltage equivalent to at least V_{BE} (which is a voltage higher than V_{in}) through a set of switches in the bandgap reference circuit (e.g., switched capacitor charge pump circuits, reference generation circuit, etc.) to generate the desired bandgap reference voltage (V_{REF}). This is because closing a switch to pass a voltage involves inherent voltage loss within the source-drain of the transistors of the switch. Hence, for passing a voltage of V_{BE} through a switch, the clock signal has to sweep to a voltage value greater than V_{BE}. Otherwise if the input voltage at the gate terminal of a switch (e.g., an NMOS switch) is lower than the voltage value (or voltage level) that the switch has to pass, the switch cannot pass the full voltage

(V_{BE}). As a result, in some instances, the clock signal being generated from the oscillator (e.g., oscillator **1120** in FIG. **11**) undergoes signal boosting or enhancement (e.g., via a clock doubler) before being sent to the bandgap reference circuit as discussed in greater detail below.

FIGS. **13**A-B are schematic illustrations of an implementation of switches for the bandgap reference circuit shown in FIG. **4**. FIG. **13**A shows the switched capacitor charge pump circuit **410** in electrical connection with the base-emitter voltage clamp circuit **415** (that includes BJT Q**1** and the capacitor C_L). FIG. **13**B shows an implementation of one of the switch **417** associated with the clock phase signal ϕ_2. The switch **417** is implemented using a transmission gate including transistors (metal-oxide field effect transistors (MOSFETs)) M_{NS} and M_{PS}. In some embodiments, the voltage V_{BE2} is typically clamped by the BJT Q**1** around 0.7-0.8V. In some embodiments, a clock phase signal ϕ_2 running on the magnitude V_{in} cannot be used to close the switch **417**. In such embodiments, the clock phase signal ϕ_2 swings to a magnitude of at least $2*V_{in}$ to enable the transmission gate to pass the terminal voltage V_D properly into V_{BE2} (because of inherent losses within source-drain of the transistors M_{NS} and M_{PS} within the transmission gate). Therefore, in such instances, a clock doubling circuit is implemented to convert a clock phase signal that swings from 0 to V_{in} into a clock phase signal that swings from $0>V_{BE2}$ (e.g., $2*V_{in}$ in this example).

FIGS. **14**A-C are schematic illustrations of the steps involved in implementing a clock doubling technique to generate clock signals at different phases that swings from 0 to $2V_{in}$, according to an embodiment. The steps involved in clock doubling as shown in FIGS. **14**A-C are implemented in the clock doubler of the clock circuit (e.g., clock doubler **1130** shown in the FIG. **11**). FIG. **14**A shows a first circuit portion **1410** that can generate non-overlapping clock phase signals. In FIG. **14**A, the first circuit portion **1410** receives from an on-chip clock a clock signal (e.g., CLK) having an input voltage. The first circuit portion **1410** produces a first clock phase signal (e.g., p_1) having a minimal voltage (e.g., 0) and a maximum voltage (e.g., V_{in}). Similarly, the first circuit portion **1410** also produces a second clock phase signal (e.g., p_2) that is non-overlapping with the first clock phase signal and having a minimal voltage (e.g., 0) and a maximum voltage (e.g., V_{in}). Said in another way, the first circuit portion generates two non-overlapping signals that swing from 0 to V_{in}. The signals p_1 and p_2 can be seen as being non-overlapping because at any time (i.e., during any T) when the signal p_1 has an amplitude of zero, the signal p_2 has an amplitude of V_{in}.

The signals **p1** and **p2** will be used to generate new signals that swing from V_{in} to $2V_{in}$ using the second circuit portion as shown in FIG. **14**B. In FIG. **14**B, a second circuit portion (represented in FIG. **14**B as two sub-portions **1430** and **1435**) is operatively coupled to the first circuit portion **1410**, where the second circuit portion **1430** and **1435** includes a set of capacitors and a set of invertors that are collectively configured to output a third clock phase signal (e.g., signal represented at x_1) and a fourth clock phase signal (e.g., signal represented at x_2). The third clock phase signal (e.g., x_1) and the fourth clock phase signal (e.g., x_2) each has a minimal voltage (e.g., V_{in}) that is greater than the minimum voltage of the first clock phase signal (e.g., 0) and the minimal voltage of the second clock phase signal (e.g., 0). Additionally, the third clock phase signal (x_1) and the fourth clock phase signal (x_2) each has a maximum voltage (e.g., $2V_{in}$) that is greater than the maximum voltage of the first clock phase signal (V_{in}) and the maximum voltage of the second clock phase signal (V_{in}). In FIG. **14**B, the node xb_1 (shown in sub-portion **1430**) and the node xb_2 (shown in sub-portion **1435**) are the output of inverters running on V_{in} and thus the voltage at nodes xb_1 and xb_2 swing from 0 to V_{in}. Node x_1 (in sub-portion **1430**) and node x_2 (in sub-portion **1435**) are connected through diode-connected NMOS transistors to a capacitor. The transistors used are low threshold voltage (L_{VT}) transistors, and hence in the absence of a load, nodes x_1 and x_2 will charge to V_{in}, because the L_{VT} transistors have high leakage. Furthermore, the bottom plate of the capacitors connected to node x_1 and x_2 swing from 0 to V_{in}. Therefore, the top plate of such capacitors will swing from V_{in} to $2V_{in}$ resulting in the signals represented at x_1 and at x_2 respectively in the chart of FIG. **14**B.

The signals represented at x_1 and at x_2 respectively in FIG. **14**B are transformed into signals that can swing from 0 to $2*V_{in}$ using the third circuit portion shown in FIG. **14**C. In FIG. **14**C, a third circuit portion (represented in FIG. **14**C as two sub-portions **1450** and **1455**) is operatively coupled to the second circuit portion (**1430** and **1435** in FIG. **14**B). The third circuit portion **1450** and **1455** includes a set of transistors that can output a fifth clock phase signal (e.g., represented as ϕ_1) and a sixth clock phase signal (e.g., represented as ϕ_2). Furthermore, the fifth clock phase signal (ϕ_1) and the sixth clock phase signal (ϕ_2) each has a minimal voltage substantially equal to the minimum voltage of the first clock phase signal (**0**) and the minimal voltage of the second clock phase signal (**0**), and the fifth clock phase signal (ϕ_1) and the sixth clock phase signal (ϕ_2) each have a maximum voltage ($2*V_{in}$) substantially equal to the maximum voltage of the third clock phase signal (x_1) ($2*V_{in}$) and the maximum voltage of the fourth clock phase signal (x_2) ($2*V_{in}$). In FIG. **14**C, in the third circuit sub-portion **1450**, when the voltage at p_1 is high, the voltage at x_2 is also high, and thus the net voltage of the phase signal (ϕ_1) is pulled down to ground. When the voltage at p_1 is zero, the voltage at x_2 is low at V_{in}. At this time, the voltage at x_1 is at $2*V_{in}$. At this time the PMOS transistor turns on and passes the x_1 voltage level to the clock phase signal ϕ_1. As a result, the clock phase signal ϕ_1 swings from 0 to $2*V_{in}$. Similarly, the clock phase signal ϕ_2 also swings from 0 to $2*V_{in}$ in a non-overlapping manner as shown in the chart in FIG. **14**C.

FIGS. **15**A-B present the results of simulations of an example of a clock doubler circuit that sends boosted clock phase signals to a bandgap voltage reference circuit. FIG. **15**A shows that the signal p_2 (similar to the phase signal p**2** in FIG. **14**A) swings from 0 to 400 mV in time (i.e., swings from 0 to V_{in}). FIG. **15**A also shows that the signal x_1 (similar to the phase signal x_1 in FIG. **14**B) swings from 350 mV to 750 mV in time (i.e., approximately swings from V_{in} to $2*V_{in}$). FIG. **15** B shows that the signal phi_2 (similar to the phase signal ϕ_2 in FIG. **14**C) swings from 0 to 750 mV in time (i.e., approximately swings from 0 to $2*V_{in}$).

Referring to FIGS. **3**, **4** and **14**, in some configurations of a bandgap voltage reference circuit system, a first switched capacitor charge pump (e.g., switched capacitor charge pump **410** in FIG. **4**) (or simply a first charge pump) is operatively coupled to the clock circuit (e.g., clock circuit **335** in FIG. **3**) and a first BJT of the bandgap reference circuit (e.g. BJT Q**1** in FIG. **4**). In such configurations, the first switched capacitor charge pump can receive the fifth clock phase signal (e.g., clock phase signal ϕ_1 in FIG. **14**C) and the sixth clock phase signal (e.g., clock phase signal ϕ_2 in FIG. **14**C) and output a voltage driving the terminal of the first BJT (e.g. BJT Q**1** in FIG. **4**). Similarly, in such configurations, a second switched capacitor charge pump

(e.g., switched capacitor charge pump **420** in FIG. **4**) (or simply a second charge pump) is operatively coupled to the clock circuit (e.g., clock circuit **335** in FIG. **3**) and a second BJT of the bandgap reference circuit (e.g. BJT Q**2** in FIG. **4**). In such configurations, the second switched capacitor charge pump can receive the fifth clock phase signal (e.g., clock phase signal ϕ_1 in FIG. **14**C) and the sixth clock phase signal (e.g., clock phase signal ϕ_2 in FIG. **14**C) and output a voltage driving the terminal of the first BJT (e.g. BJT Q**1** in FIG. **4**).

Also referring to FIGS. **3**, **4** and **14**, the clock circuit (e.g., clock circuit **335** in FIG. **3**) sends a clock signal with a specific frequency to the bandgap voltage reference circuit (e.g., bandgap voltage reference circuit **305** in FIG. **3**). In such configurations, a first switched capacitor charge pump (e.g., switched capacitor charge pump **410** in FIG. **4**) (or simply a first charge pump) is operatively coupled to the clock circuit (e.g., clock circuit **335** in FIG. **3**) and a first BJT of the bandgap reference circuit (e.g. BJT Q**1** in FIG. **4**). In such configurations, the first switched capacitor charge pump can output a voltage (i.e., voltage at node A in FIG. **4**) driving the terminal of the first BJT based on the fifth clock phase signal (e.g., clock phase signal ϕ_1 in FIG. **14**C) and the sixth clock phase signal (e.g., clock phase signal ϕ_2 in FIG. **14**C), where the frequency of the fifth clock phase signal and the sixth clock phase signal varies inversely with the input voltage of the first BJT (i.e., voltage at node A in FIG. **4**). Similarly, in such configurations, a second switched capacitor charge pump (e.g., switched capacitor charge pump **420** in FIG. **4**) (or simply a second charge pump) is operatively coupled to the clock circuit (e.g., clock circuit **335** in FIG. **3**) and a second BJT of the bandgap reference circuit (e.g. BJT Q**2** in FIG. **4**). In such configurations, the second switched capacitor charge pump can output a voltage (i.e., voltage at node B in FIG. **4**) driving the terminal of the second BJT based on the fifth clock phase signal (e.g., clock phase signal ϕ_1 in FIG. **14**C) and the sixth clock phase signal (e.g., clock phase signal ϕ_2 in FIG. **14**C), where the frequency of the fifth clock phase signal and the sixth clock phase signal varies inversely with the input voltage of the second BJT (i.e., voltage at node B in FIG. **4**).

FIG. **16** shows the annotated lay out of the complete bandgap reference circuit, according to an embodiment. The bandgap voltage reference circuit shown in FIG. **16** has an area of 0.0264 mm^2 and can be implemented, for example, in a commercial bulk 130 nm complementary metal-oxide-semiconductor (CMOS) process or other types of suitable technologies. The capacitors are implemented using nMOS (or n-channel MOSFET) capacitors and metal-insulator-metal (MIM) capacitors. The load capacitors for the V_{BE} generation circuit and the V_{BE} fraction generation switched capacitor circuit (see circuits in FIG. **9**) were implemented using nMOS capacitors, whereas the load capacitors for the bandgap output generation (see circuit in FIG. **10**) and the ΔV_{BE} doubling circuit (see circuit in FIG. **8**) were implemented using MIM capacitors to avoid bottom plate capacitor parasitics. The total area of the bandgap voltage reference circuit as shown in FIG. **16** is significantly smaller than known low power bandgap reference circuits because the bandgap voltage reference circuit shown in FIG. **16** does not use large resistors. The bandgap voltage reference circuit shown in FIG. **16** also consumes 19.2 nW of power at 0.4V V_{in}, which is an order of magnitude lower than the power used in known non-duty-cycled bandgap reference circuits.

Because the bandgap reference circuit is a switching capacitor circuit, the bandgap reference circuit has a settling time at startup. FIG. **17** is a graphical display of an example of the transient behavior of a bandgap reference circuit at start-up. FIG. **17** shows the bandgap reference circuit takes 15 msec to settle at a 0.8V V_{in}. At 0.4V, the settling time is 90 msec. The settling time is directly dependent on the clock frequency and the power supply V_{in}. In some configurations, the settling time for the bandgap reference circuit can be large. In such configurations, a fast start-up mode for the bandgap reference circuit can be implemented. In such configurations, during the fast start-up mode, the clock frequency can be made several times faster than during a normal operational mode, which can reduce the settling time of the bandgap reference circuit. This can be done during power on the fast start-up mode, where the current source of the clock source (e.g., clock circuit **335** in FIG. **3**) is increased several times which then increases the clock frequency. A settling time of 20 μs during startup of the bandgap reference circuit can be used in the fast start-up mode.

An embodiment of the bandgap reference circuit was verified for proper functionality in the temperature range of −20° C. to 100° C. While this range is quite large for the intended ULP applications, the performance of the bandgap reference circuit in this range is relevant as it compares with known state-of-the-art bandgap reference circuits. FIG. **18** shows the simulated variation of an embodiment of a bandgap reference circuit output for a temperature range of −20° C. to 100° C. The bandgap reference circuit can provide an output voltage of 500 mV and the output voltage varies by 3 mV over a temperature variation of 120° C., thus achieving a performance of 50 ppm/° C. The performance of such a bandgap reference circuit with temperature as shown in FIG. **20** is in line with known technologies and an improved performance can be achieved at a higher output voltage (i.e., output voltage >500 mV).

FIG. **19** presents the results of a Monte-Carlo simulation that shows an example of the change in bandgap reference output with respect to process and mismatch variation. FIG. **19** shows the untrimmed output of the bandgap reference circuit, where the output achieves a mean (μ) of 508 mV and a standard deviation (σ) of 5 mV. The untrimmed output of the bandgap reference circuit also shows a 3σ variation of <3%. The variation in the output (voltage) shown in FIG. **19** can be reduced by trimming the bandgap output using the capacitors used in the switched capacitor circuits (see FIGS. **8**-**10**) to generate the appropriate constants for the bandgap reference output.

FIG. **20** presents the results of a simulation that shows an example of the change in bandgap reference voltage with respect to variation with input voltage (V_{in}). FIG. **20** shows the variation of input voltage (V_{in}) from two separate sources, namely an external clock and an on-chip clock. FIG. **20** shows that the bandgap reference voltage varies by approximately 4% when an external constant clock source is used to deliver V_{in}, and the bandgap reference voltage varies by approximately 2% when an on-chip cock is used to deliver V_{in}. Thus the use of an on-chip clock as discussed in the specifications thus far reduces the bandgap reference circuit output variance by approximately 50%.

The bandgap reference circuit discussed herein operates from a minimum input voltage of 0.4V, thus improving over two-fold from the known bandgap reference circuits. The power consumption of the proposed bandgap reference circuit is 19.2 nW, which is over nine-fold lower than achieved without duty cycling in known bandgap reference circuits. Known bandgap reference circuits typically achieve a low power of 170 nW by sampling the reference voltage on a capacitor by periodically turning it on and off. Duty cycling can be applied to one or more bandgap reference

circuit embodiments described herein as well to further lower power. The power supply variation can be higher in the one or more bandgap reference circuit embodiments described herein because the architecture does not use external current sources, which are typically used in known architectures. The lower area of the bandgap reference circuit (0.0264 mm^2) is also achieved because large resistors are not used.

Note that the BJT's used in the bandgap reference circuit discussed above has been shown to be a PNP BJT as an example only, and not a limitation. In other configurations, the BJT's used in the bandgap reference circuit can be an NPN BJT(s). In such configurations (i.e., during use of an NPN BJT(s)), the bandgap reference circuit can generate a temperature insensitive bandgap reference voltage (V_{REF}) using an input (supply) voltage that is lower than the base-emitter voltage (V_{BE}) of the NPN BJT. Note the term base-emitter voltage (V_{BE}) is intended to cover both the base-emitter voltage for an NPN BJT and the emitter-base voltage for a PNP BJT. The bandgap reference circuits described thus far can be implemented using both PNP BJT's as well as NPN BJT's. Furthermore, the bandgap reference circuits using PNP BJT's can be fabricated using a CMOS process, and the bandgap reference circuits using NPN BJT's can be fabricated using biCMOS or other processes.

While various embodiments have been described above, it should be understood that they have been presented by way of example only, and not limitation. Where methods described above indicate certain events occurring in certain order, the ordering of certain events may be modified. Additionally, certain of the events may be performed concurrently in a parallel process when possible, as well as performed sequentially as described above. Likewise, the various diagrams may depict an example architectural or other configuration for the invention, which is done to aid in understanding the features and functionality that can be included in the invention. The invention is not restricted to the illustrated example architectures or configurations, but can be implemented using a variety of alternative architectures and configurations. Additionally, although the invention is described above in terms of various exemplary embodiments and implementations, it should be understood that the various features and functionality described in one or more of the individual embodiments are not limited in their applicability to the particular embodiment with which they are described, but instead can be applied, alone or in some combination, to one or more of the other embodiments of the invention, whether or not such embodiments are described and whether or not such features are presented as being a part of a described embodiment. Thus the breadth and scope of the present invention should not be limited by any of the above-described exemplary embodiments.

What is claimed is:

1. An apparatus, comprising:

a bandgap reference circuit having:

a first bipolar junction transistor (BJT) configured to generate a base emitter voltage of the first BJT based on a first input voltage of the first BJT that is lower than the base emitter voltage of the first BJT, the first input voltage being generated by a first charge pump;

a second bipolar junction transistor (BJT) having a device width greater than a device width of the first BJT, the second BJT configured to generate a base emitter voltage of the second BJT based on a second input voltage of the second BJT that is lower than the base emitter voltage of the second BJT, the second input voltage being generated by a second charge pump; and

a reference generation circuit operatively coupled to the first BJT and the second BJT, the reference generation circuit configured to generate a bandgap reference voltage based on the base emitter voltage of the first BJT and the base emitter voltage of the second BJT.

2. The apparatus of claim **1**, wherein:

the first BJT is configured to receive the first input voltage for the first BJT from a first power supply without generation of a first intermediate voltage that is higher than the base emitter voltage of the first BJT,

the second BJT is configured to receive the second input voltage for the second BJT from a second power supply without generation of a second intermediate voltage that is higher than the base emitter voltage of the second BJT.

3. The apparatus of claim **1**, wherein:

the first BJT is operatively coupled to the first charge pump circuit via at least a first capacitor,

the second BJT is operatively coupled to the second charge pump circuit via at least a second capacitor.

4. The apparatus of claim **1**, further comprising:

a clock circuit operatively coupled to the bandgap reference circuit;

the bandgap reference circuit further having:

the first charge pump circuit operatively coupled to the first BJT and the clock circuit, the first charge pump circuit configured to receive the first input voltage of the first BJT and to output the base emitter voltage of the first BJT, the first input voltage for the first charge pump circuit being less than the first input voltage of the first BJT; and

the second charge pump circuit operatively coupled to the second BJT and the clock circuit, the second charge pump configured to receive the second input voltage of the second BJT and to output the base emitter voltage of the second BJT, the second input voltage for the second charge pump circuit being less than the second input voltage of the second BJT.

5. The apparatus of claim **1**, further comprising:

a clock circuit operatively coupled to the bandgap reference circuit, the clock circuit configured to send a clock signal having a frequency;

the frequency of the clock signal sent by the clock circuit varying inversely with the first input voltage of the first BJT.

6. The apparatus of claim **1**, further comprising:

a clock circuit operatively coupled to the bandgap reference circuit, the clock circuit configured to send a clock signal having a first clock phase and a second clock phase,

the bandgap reference circuit further having:

the first charge pump circuit operatively coupled to the first BJT and the clock circuit, the first charge pump having a first configuration when receiving the first clock phase of the clock signal and a second configuration when receiving the second clock phase of the clock signal, the first charge pump configured to output the base emitter voltage of the first BJT based on a first charge stored at a first capacitor during the first configuration and the second configuration of the first charge pump,

the second charge pump circuit operatively coupled to the second BJT and the clock circuit, the second charge pump having a first configuration when receiving the first clock phase of the clock signal and

a second configuration when receiving the second clock phase of the clock signal, the second charge pump configured to output the base emitter voltage of the second BJT based on a second charge stored at a second capacitor during the first configuration and the second configuration of the second charge pump.

7. The apparatus of claim **1**, wherein:

the reference generation circuit has a plurality of switched capacitors without including or being operatively coupled to a current mirror that sources current from a node at a voltage higher than (1) the base emitter voltage of the first BJT, and (2) the base emitter voltage of the second BJT.

8. The apparatus of claim **1**, wherein:

the reference generation circuit includes a capacitor operatively coupled to a first BJT and a second BJT, the capacitor storing a difference of the base emitter voltage of the first BJT and the base emitter voltage of the second BJT when the first BJT and the second BJT are operating.

9. The apparatus of claim **1**, wherein:

the reference generation circuit has a first configuration and a second configuration,

the reference generation circuit in the first configuration having a plurality of switched capacitors in a first arrangement to define a first scaled base emitter voltage based on the base emitter voltage of the first BJT, which decreases with temperature, and a capacitance of each capacitor from the plurality of capacitors,

the reference generation circuit in the second configuration having the plurality of switched capacitors in a second arrangement to define a second scaled difference voltage based on the base emitter voltage of the second BJT, which increases with temperature, and the capacitance of each capacitor from the plurality of capacitors,

the bandgap reference voltage being substantially constant and based on the scaled base emitter voltage and the scaled difference voltage, when the bandgap reference circuit is operational.

10. An apparatus, comprising:

a reference generation circuit including:

a base-emitter fractional voltage generation circuit having:

a first capacitor connected to a bipolar junction transistor (BJT) and configured to receive a base emitter voltage from the BJT, while the base-emitter fractional voltage generation circuit is in a first configuration; and

a second capacitor connected to ground and not to the first capacitor, while the base-emitter fractional voltage generation circuit is in the first configuration;

the first capacitor connected to the second capacitor to generate a fraction of the base emitter voltage such that a bandgap voltage for the base-emitter fractional voltage generation circuit is generated, while the base-emitter fractional voltage generation circuit is in a second configuration;

a value of at least one of the first capacitor or the second capacitor is selected such that temperature compensation is performed when the base-emitter fractional voltage generation circuit is operational,

a first base-emitter voltage clamp operatively coupled to the base-emitter fractional voltage generation circuit;

a first charge pump circuit operatively coupled to the first base-emitter voltage clamp;

a second base-emitter voltage clamp operatively coupled to the base-emitter fractional voltage generation circuit; and

a second charge pump circuit operatively coupled to the second base-emitter voltage clamp.

11. The apparatus of claim **10**, further comprising:

a first switch disposed between the first capacitor and a node associated with receiving the base emitter voltage from the BJT; and

a second switch disposed between the second capacitor and ground,

the first switch and the second switch being closed while the base-emitter fractional voltage generation circuit is in the first configuration and in the second configuration, respectively.

12. The apparatus of claim **10**, further comprising:

a first switch disposed between the first capacitor and the second capacitor; and

a second switch disposed between the second capacitor and a load capacitor associated with an output of the base-emitter fractional voltage generation circuit,

the first switch and the second switch being open while the base-emitter fractional voltage generation circuit is in the first configuration and in the second configuration, respectively.

13. An apparatus, comprising:

a voltage supply circuit having:

a current source,

an oscillator operatively coupled to the current source, and

a capacitor operatively coupled to the current source and the oscillator,

the current source, the oscillator and the capacitor collectively configured to generate a local supply; and

a bandgap reference circuit operatively coupled to the local supply, the bandgap reference having:

a first bipolar junction transistor (BJT) configured to generate a base emitter voltage of the first BJT based on the local supply;

a second bipolar junction transistor (BJT) having a device width greater than a device width of the first BJT, the second BJT configured to generate a base emitter voltage of the second BJT based on the local supply; and

a reference generation circuit operatively coupled to the first BJT and the second BJT, the reference generation circuit configured to generate a bandgap reference voltage based on the base emitter voltage of the first BJT and the base emitter voltage of the second BJT,

the capacitor is included within a circuit that has a first circuit portion, a second circuit portion and a third circuit portion,

the first circuit portion configured to receive a current from the local supply and output a first signal, the first signal having two non-overlapping phases and a voltage range substantially between zero and an input voltage of the circuit,

the second circuit portion configured to receive the first signal and output a second signal, the second signal having a voltage range substantially

between the input voltage of the circuit and double the input voltage of the circuit, and

the third circuit portion configured to receive the second signal and output a third signal, the third signal having a voltage range substantially between zero and double the input voltage of the circuit.

14. The apparatus of claim **13**, wherein the oscillator is a current-controlled ring oscillator configured to receive the current from the local supply, the current configured to be temperature dependent but substantially independent of an input voltage of the first BJT and/or the second BJT.

15. The apparatus of claim **13**, wherein the capacitor is within a clock doubler configured to double a voltage sweep range of the local supply, the local supply having two non-overlapping clock phases.

16. The apparatus of claim **13**, wherein the bandgap reference circuit further has:

a first charge pump circuit operatively coupled to the first BJT and the current source; and

a second charge pump circuit operatively coupled to the second BJT and the current source.

17. The apparatus of claim **13**, wherein the bandgap reference circuit further has:

a first charge pump circuit operatively coupled to the first BJT and the current source, the first charge pump circuit configured to receive an input voltage from the current source and to output the base emitter voltage of the first BJT, the input voltage for the first charge pump circuit being less than the base emitter voltage of the first BJT; and

a second charge pump circuit operatively coupled to the second BJT and the current source, the second charge pump configured to receive an input voltage from the current source and to output the base emitter voltage of the second BJT, the input voltage for the second charge pump circuit being less than the base emitter voltage of the second BJT.

18. The apparatus of claim **13**, wherein the bandgap reference circuit further has:

a first charge pump circuit operatively coupled to the first BJT and the current source, the first charge pump having a first configuration when receiving a first phase of the local supply and a second configuration when receiving a second phase of the local supply, the first charge pump configured to output the base emitter voltage of the first BJT based on a first charge stored at a first capacitor during the first configuration and the second configuration of the first charge pump; and

a second charge pump circuit operatively coupled to the second BJT and the current source, the second charge pump having a first configuration when receiving the first phase of the local supply and a second configuration when receiving the second phase of the local supply, the second charge pump configured to output the base emitter voltage of the second BJT based on a second charge stored at a second capacitor during the first configuration and the second configuration of the second charge pump.

19. An apparatus, comprising:

a bandgap reference circuit having:

a first base-emitter voltage clamp operatively coupled to a reference generation circuit, the first base-emitter voltage clamp including a first bipolar junction transistor (BJT) configured to generate a base emitter voltage of the first BJT based on a first input voltage of the first BJT that is lower than the base emitter voltage of the first BJT;

a second base-emitter voltage clamp operatively coupled to the reference generation circuit, the second base-emitter voltage clamp including a second bipolar junction transistor (BJT) having a device width greater than a device width of the first BJT, the second BJT configured to generate a base emitter voltage of the second BJT based on a second input voltage of the second BJT that is lower than the base emitter voltage of the second BJT;

a first charge pump circuit operatively coupled to the first base-emitter voltage clamp;

a second charge pump circuit operatively coupled to the second base-emitter voltage clamp; and

the reference generation circuit operatively coupled to the first BJT and the second BJT, the reference generation circuit configured to generate a bandgap reference voltage based on the base emitter voltage of the first BJT and the base emitter voltage of the second BJT.

20. The apparatus of claim **1**, wherein:

the first input voltage is no greater than half of the base emitter voltage of the first BJT, and/or

the second input voltage is no greater than half of the base emitter voltage of the second BJT.

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